

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

SLVS132E – NOVEMBER 1995 – REVISED OCTOBER 2002

- Industry-Standard Driver Replacement
- 25-ns Max Rise/Fall Times and 40-ns Max Propagation Delay – 1-nF Load, $V_{CC} = 14\text{ V}$
- 2-A Peak Output Current, $V_{CC} = 14\text{ V}$
- 5- μA Supply Current — Input High or Low
- 4-V to 14-V Supply-Voltage Range; Internal Regulator Extends Range to 40 V (TPS2811, TPS2812, TPS2813)
- -40°C to 125°C Ambient-Temperature Operating Range

description

The TPS28xx series of dual high-speed MOSFET drivers are capable of delivering peak currents of 2 A into highly capacitive loads. This performance is achieved with a design that inherently minimizes shoot-through current and consumes an order of magnitude less supply current than competitive products.

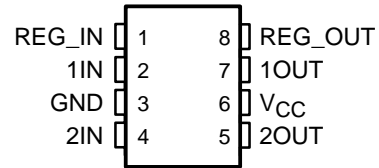
The TPS2811, TPS2812, and TPS2813 drivers include a regulator to allow operation with supply inputs between 14 V and 40 V. The regulator output can power other circuitry, provided power dissipation does

not exceed package limitations. When the regulator is not required, REG_IN and REG_OUT can be left disconnected or both can be connected to V_{CC} or GND.

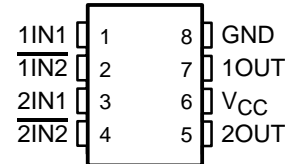
The TPS2814 and the TPS2815 have 2-input gates that give the user greater flexibility in controlling the MOSFET. The TPS2814 has AND input gates with one inverting input. The TPS2815 has dual-input NAND gates.

TPS28xx series drivers, available in 8-pin PDIP, SOIC, and TSSOP packages and as unmounted ICs, operate over a ambient temperature range of -40°C to 125°C .

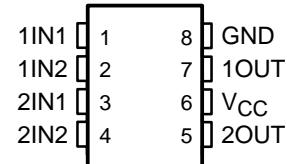
TPS2811, TPS2812, TPS2813 . . . D, P, AND PW PACKAGES (TOP VIEW)



TPS2814 . . . D, P, AND PW PACKAGES (TOP VIEW)



TPS2815 . . . D, P, AND PW PACKAGES (TOP VIEW)



AVAILABLE OPTIONS

| T _A | INTERNAL REGULATOR | LOGIC FUNCTION | PACKAGED DEVICES | | | CHIP FORM (Y) |
|--|--------------------|--|-------------------|-----------------|-------------|---------------|
| | | | SMALL OUTLINE (D) | PLASTIC DIP (P) | TSSOP (PW) | |
| -40°C to 125°C | Yes | Dual inverting drivers | TPS2811D | TPS2811P | TPS2811PWLE | TPS2811Y |
| | | Dual noninverting drivers | TPS2812D | TPS2812P | TPS2812PWLE | TPS2812Y |
| | | One inverting and one noninverting driver | TPS2813D | TPS2813P | TPS2813PWLE | TPS2813Y |
| | No | Dual 2-input AND drivers, one inverting input on each driver | TPS2814D | TPS2814P | TPS2814PWLE | TPS2814Y |
| Dual 2-input NAND drivers | | TPS2815D | TPS2815P | TPS2815PWLE | TPS2815Y | |

The D package is available taped and reeled. Add R suffix to device type (e.g., TPS2811DR). The PW package is only available left-end taped and reeled and is indicated by the LE suffix on the device type (e.g., TPS2811PWLE).



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

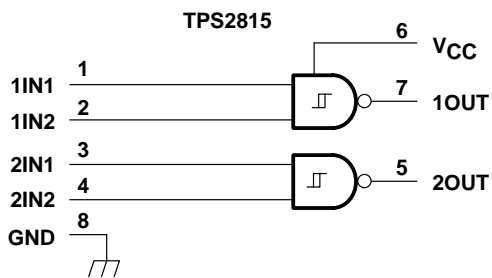
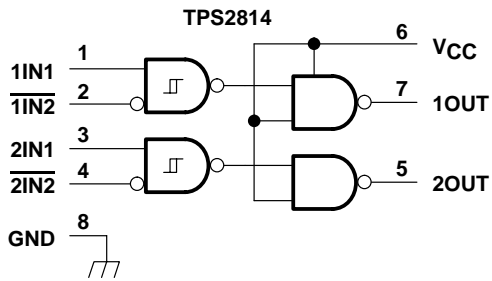
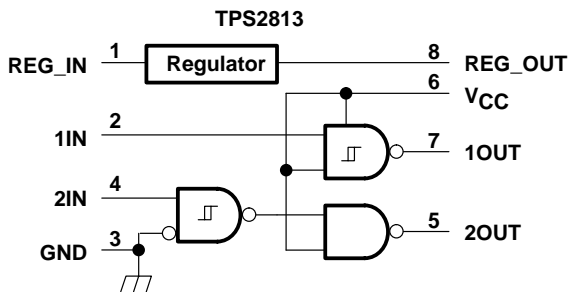
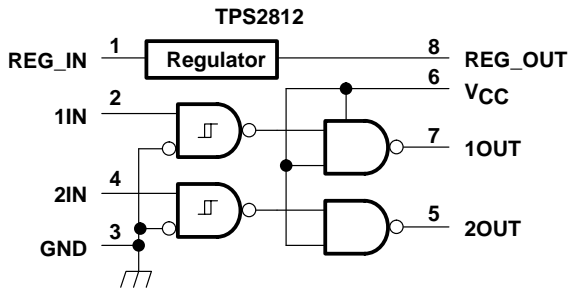
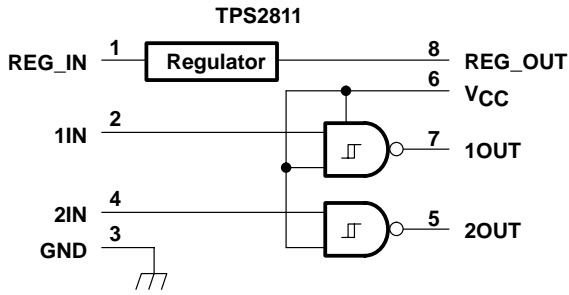
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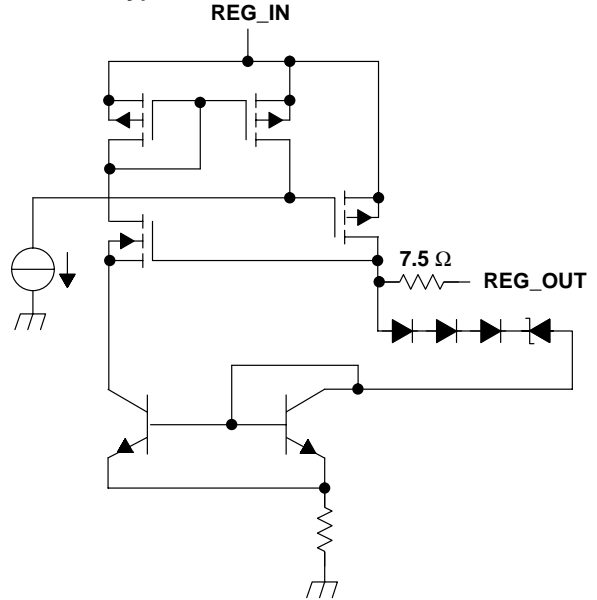
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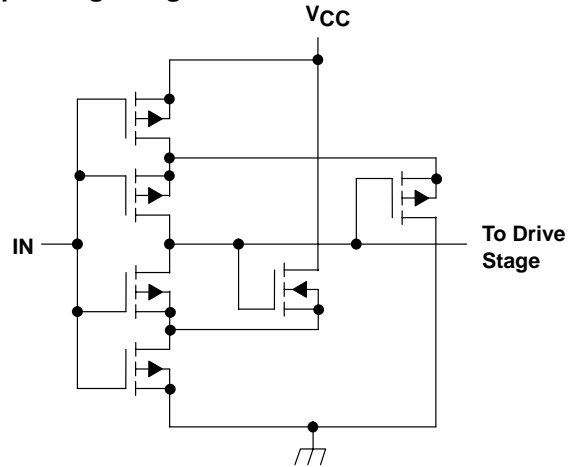
functional block diagram



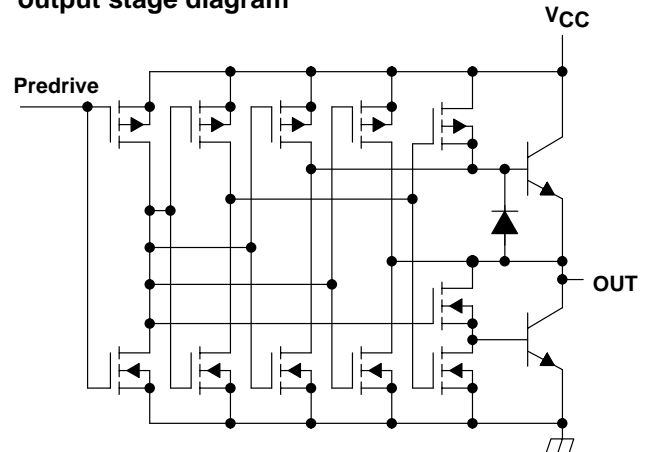
regulator diagram (TPS2811, TPS2812, TPS2813 only)



input stage diagram



output stage diagram

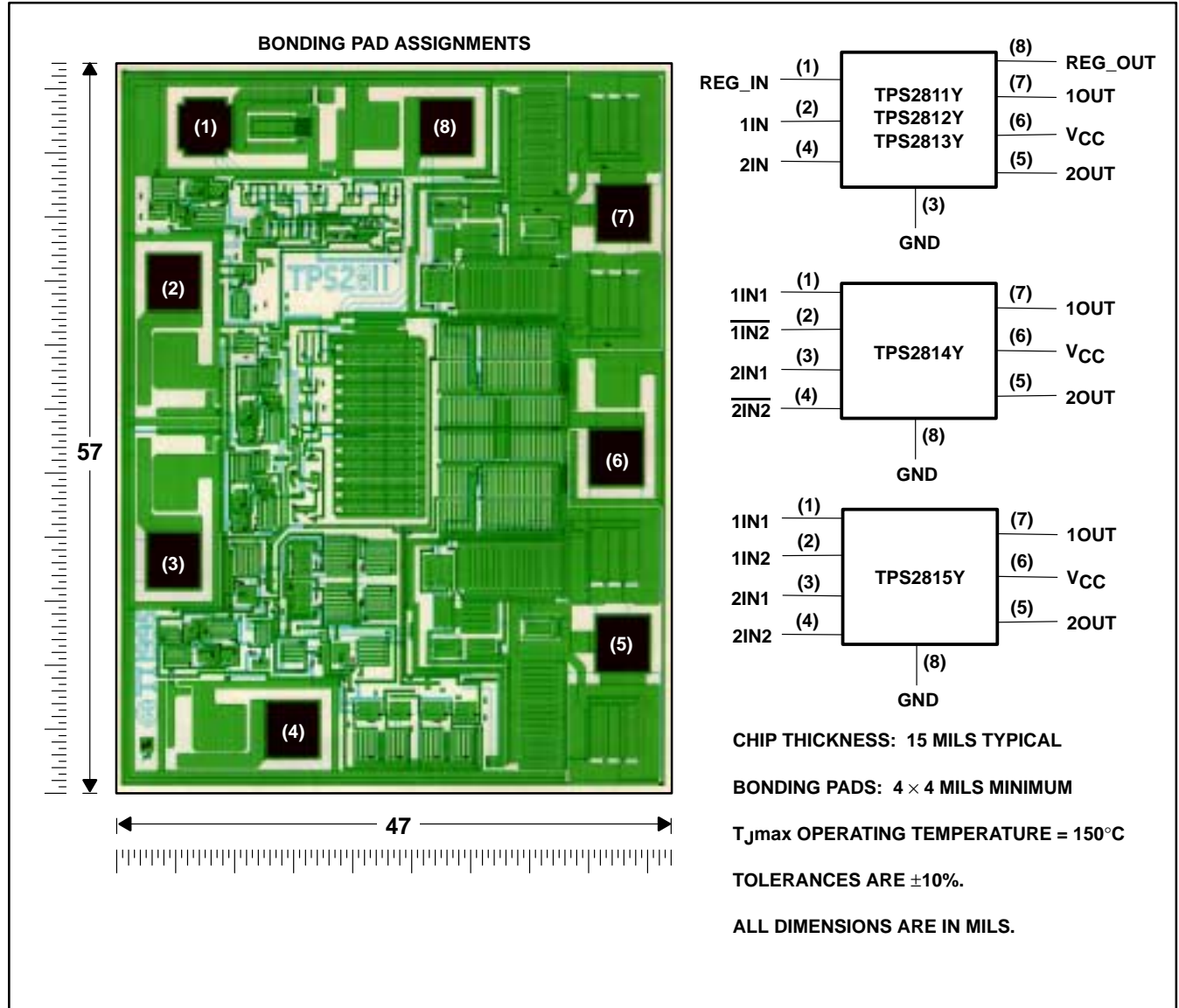


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TPS28xxY chip information

This chip, when properly assembled, displays characteristics similar to those of the TPS28xx. Thermal compression or ultrasonic bonding may be used on the doped aluminum bonding pads. The chip may be mounted with conductive epoxy or a gold-silicon preform.



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Terminal Functions

TPS2811, TPS2812, TPS2813

| TERMINAL NAME | TERMINAL NUMBERS | | | DESCRIPTION |
|---------------|--------------------------------------|---|-------------------------------------|------------------|
| | TPS2811 Dual Inverting Drivers | TPS2812 Dual Noninverting Drivers | TPS2813 Complimentary Drivers | |
| REG_IN | 1 | 1 | 1 | Regulator input |
| 1IN | 2 | 2 | 2 | Input 1 |
| GND | 3 | 3 | 3 | Ground |
| 2IN | 4 | 4 | 4 | Input 2 |
| 2OUT | 5 = $\overline{2IN}$ | 5 = 2IN | 5 = 2IN | Output 2 |
| VCC | 6 | 6 | 6 | Supply voltage |
| 1OUT | 7 = $\overline{1IN}$ | 7 = 1IN | 7 = $\overline{1IN}$ | Output 1 |
| REG_OUT | 8 | 8 | 8 | Regulator output |

TPS2814, TPS2815

| TERMINAL NAME | TERMINAL NUMBERS | | DESCRIPTION |
|-------------------|--|------------------------------------|----------------------------------|
| | TPS2814 Dual AND Drivers with Single Inverting Input | TPS2815 Dual NAND Drivers | |
| 1IN1 | 1 | 1 | Noninverting input 1 of driver 1 |
| $\overline{1IN2}$ | 2 | - | Inverting input 2 of driver 1 |
| 1IN2 | - | 2 | Noninverting input 2 of driver 1 |
| 2IN1 | 3 | 3 | Noninverting input 1 of driver 2 |
| $\overline{2IN2}$ | 4 | - | Inverting input 2 of driver 2 |
| 2IN2 | - | 4 | Noninverting input 2 of driver 2 |
| 2OUT | 5 = $2IN1 \bullet \overline{2IN2}$ | 5 = $\overline{2IN1} \bullet 2IN2$ | Output 2 |
| VCC | 6 | 6 | Supply voltage |
| 1OUT | 7 = $1IN1 \bullet \overline{1IN2}$ | 7 = $\overline{1IN1} \bullet 1IN2$ | Output 1 |
| GND | 8 | 8 | Ground |

DISSIPATION RATING TABLE

| PACKAGE | $T_A \leq 25^\circ\text{C}$ POWER RATING | DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$ | $T_A = 70^\circ\text{C}$ POWER RATING | $T_A = 85^\circ\text{C}$ POWER RATING |
|---------|---|---|--|--|
| P | 1090 mW | 8.74 mW/°C | 697 mW | 566 mW |
| D | 730 mW | 5.84 mW/°C | 467 mW | 380 mW |
| PW | 520 mW | 4.17 mW/°C | 332 mW | 270 mW |

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

| | |
|---|------------------------------|
| Supply voltage, V_{CC} | -0.3 V to 15 V |
| Regulator input voltage range, REG_IN | $V_{CC} - 0.3$ V to 42 V |
| Input voltage range, 1IN, 2IN, 1IN1, 1IN2, 1IN2, 2IN1, 2IN2, 2IN2 | -0.3 V to $V_{CC} + 0.5$ V |
| Output voltage range, 1OUT, 2OUT | $-0.5 < V < V_{CC} + 0.5$ V |
| Continuous regulator output current, REG_OUT | 25 mA |
| Continuous output current, 1OUT, 2OUT | ± 100 mA |
| Continuous total power dissipation | See Dissipation Rating Table |
| Operating ambient temperature range, T_A | -40°C to 125°C |
| Storage temperature range, T_{stg} | -65°C to 150°C |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | 260°C |

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to device GND pin.

recommended operating conditions

| | MIN | MAX | UNIT |
|---|------|----------|------|
| Regulator input voltage range | 8 | 40 | V |
| Supply voltage, V_{CC} | 4 | 14 | V |
| Input voltage, 1IN1, 1IN2, 1IN2, 2IN1, 2IN2, 2IN2, 1IN, 2IN | -0.3 | V_{CC} | V |
| Continuous regulator output current, REG_OUT | 0 | 20 | mA |
| Ambient temperature operating range | -40 | 125 | °C |

TPS28xx electrical characteristics over recommended operating ambient temperature range, $V_{CC} = 10$ V, REG_IN open for TPS2811/12/13, $C_L = 1$ nF (unless otherwise noted)

inputs

| PARAMETER | TEST CONDITIONS | MIN | TYP† | MAX | UNIT |
|--|--------------------------|-----|------|-----|---------|
| Positive-going input threshold voltage | $V_{CC} = 5$ V | | 3.3 | 4 | V |
| | $V_{CC} = 10$ V | | 5.8 | 9 | V |
| | $V_{CC} = 14$ V | | 8.3 | 13 | V |
| Negative-going input threshold voltage | $V_{CC} = 5$ V | 1 | 1.6 | | V |
| | $V_{CC} = 10$ V | 1 | 4.2 | | V |
| | $V_{CC} = 14$ V | 1 | 6.2 | | V |
| Input hysteresis | $V_{CC} = 5$ V | | 1.6 | | V |
| Input current | Inputs = 0 V or V_{CC} | -1 | 0.2 | 1 | μ A |
| Input capacitance | | | 5 | 10 | pF |

† Typical values are for $T_A = 25^\circ\text{C}$ unless otherwise noted.

outputs

| PARAMETER | TEST CONDITIONS | MIN | TYP† | MAX | UNIT |
|---------------------------|-----------------|------|------|------|------|
| High-level output voltage | $I_O = -1$ mA | 9.75 | 9.9 | | V |
| | $I_O = -100$ mA | 8 | 9.1 | | |
| Low-level output voltage | $I_O = 1$ mA | | 0.18 | 0.25 | V |
| | $I_O = 100$ mA | | 1 | 2 | |
| Peak output current | $V_{CC} = 10$ V | | 2 | | A |

† Typical values are for $T_A = 25^\circ\text{C}$ unless otherwise noted.

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regulator (TPS2811/2812/2813 only)

| PARAMETER | TEST CONDITIONS | MIN | TYP† | MAX | UNIT |
|---------------------------|--|-----|------|-----|------|
| Output voltage | $14 \leq \text{REG_IN} \leq 40 \text{ V}$, $0 \leq I_O \leq 20 \text{ mA}$ | 10 | 11.5 | 13 | V |
| Output voltage in dropout | $I_O = 10 \text{ mA}$, $\text{REG_IN} = 10 \text{ V}$ | 9 | 9.6 | | V |

† Typical values are for $T_A = 25^\circ\text{C}$ unless otherwise noted.

supply current

| PARAMETER | TEST CONDITIONS | MIN | TYP† | MAX | UNIT |
|------------------------------|--|-----|------|-----|---------------|
| Supply current into V_{CC} | Inputs high or low | | 0.2 | 5 | μA |
| Supply current into REG_IN | $\text{REG_IN} = 20 \text{ V}$, REG_OUT open | | 40 | 100 | μA |

† Typical values are for $T_A = 25^\circ\text{C}$ unless otherwise noted.

TPS28xxY electrical characteristics at $T_A = 25^\circ\text{C}$, $V_{CC} = 10 \text{ V}$, REG_IN open for TPS2811/12/13, $C_L = 1 \text{ nF}$ (unless otherwise noted)

inputs

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--------------------------|-----|-----|-----|---------------|
| Positive-going input threshold voltage | $V_{CC} = 5 \text{ V}$ | | 3.3 | | V |
| | $V_{CC} = 10 \text{ V}$ | | 5.8 | | V |
| | $V_{CC} = 14 \text{ V}$ | | 8.2 | | V |
| Negative-going input threshold voltage | $V_{CC} = 5 \text{ V}$ | | 1.6 | | V |
| | $V_{CC} = 10 \text{ V}$ | | 3.3 | | V |
| | $V_{CC} = 14 \text{ V}$ | | 4.2 | | V |
| Input hysteresis | $V_{CC} = 5 \text{ V}$ | | 1.2 | | V |
| Input current | Inputs = 0 V or V_{CC} | | 0.2 | | μA |
| Input capacitance | | | 5 | | pF |

outputs

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------|---------------------------|-----|------|-----|------|
| High-level output voltage | $I_O = -1 \text{ mA}$ | | 9.9 | | V |
| | $I_O = -100 \text{ mA}$ | | 9.1 | | |
| Low-level output voltage | $I_O = 1 \text{ mA}$ | | 0.18 | | V |
| | $I_O = 100 \text{ mA}$ | | 1 | | |
| Peak output current | $V_{CC} = 10.5 \text{ V}$ | | 2 | | A |

regulator (TPS2811, 2812, 2813)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------|--|-----|------|-----|------|
| Output voltage | $14 \leq \text{REG_IN} \leq 40 \text{ V}$, $0 \leq I_O \leq 20 \text{ mA}$ | | 11.5 | | V |
| Output voltage in dropout | $I_O = 10 \text{ mA}$, $\text{REG_IN} = 10 \text{ V}$ | | 9.6 | | V |

power supply current

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|------------------------------|--|-----|-----|-----|---------------|
| Supply current into V_{CC} | Inputs high or low | | 0.2 | | μA |
| Supply current into REG_IN | $\text{REG_IN} = 20 \text{ V}$, REG_OUT open | | 40 | | μA |

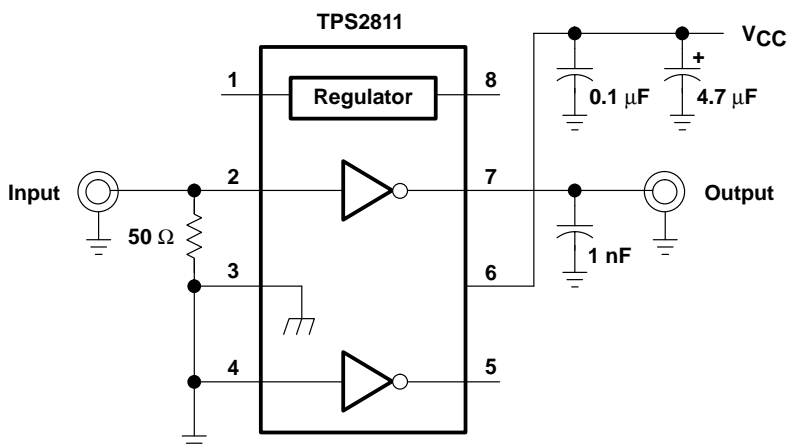
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switching characteristics for all devices over recommended operating ambient temperature range, REG_IN open for TPS2811/12/13, $C_L = 1\text{ nF}$ (unless otherwise specified)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------|--|------------------------|-----|-----|-----|------|
| t_r | Rise time | $V_{CC} = 14\text{ V}$ | | 14 | 25 | ns |
| | | $V_{CC} = 10\text{ V}$ | | 15 | 30 | |
| | | $V_{CC} = 5\text{ V}$ | | 20 | 35 | |
| t_f | Fall time | $V_{CC} = 14\text{ V}$ | | 15 | 25 | ns |
| | | $V_{CC} = 10\text{ V}$ | | 15 | 30 | |
| | | $V_{CC} = 5\text{ V}$ | | 18 | 35 | |
| t_{PHL} | Prop delay time high-to-low-level output | $V_{CC} = 14\text{ V}$ | | 25 | 40 | ns |
| | | $V_{CC} = 10\text{ V}$ | | 25 | 45 | |
| | | $V_{CC} = 5\text{ V}$ | | 34 | 50 | |
| t_{PLH} | Prop delay time low-to-high-level output | $V_{CC} = 14\text{ V}$ | | 24 | 40 | ns |
| | | $V_{CC} = 10\text{ V}$ | | 26 | 45 | |
| | | $V_{CC} = 5\text{ V}$ | | 36 | 50 | |

PARAMETER MEASUREMENT INFORMATION



NOTE A: Input rise and fall times should be $\leq 10\text{ ns}$ for accurate measurement of ac parameters.

Figure 1. Test Circuit For Measurement of Switching Characteristics

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PARAMETER MEASUREMENT INFORMATION

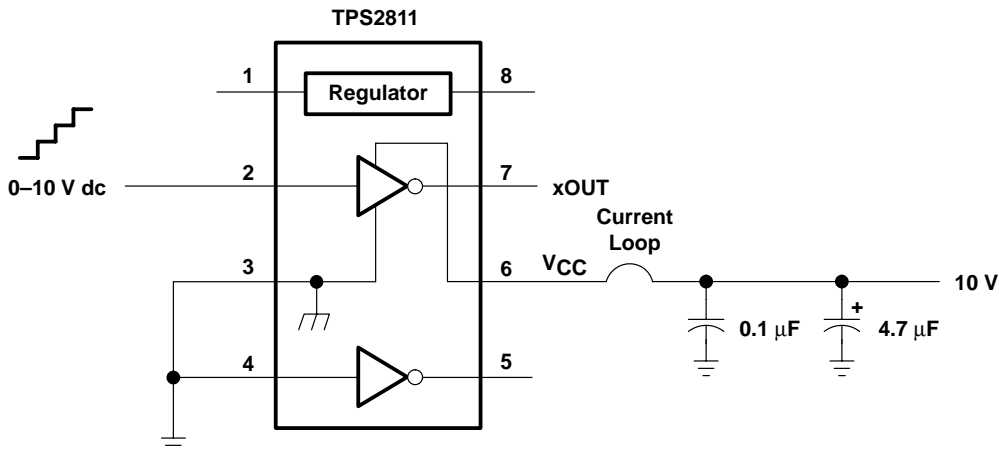


Figure 2. Shoot-through Current Test Setup

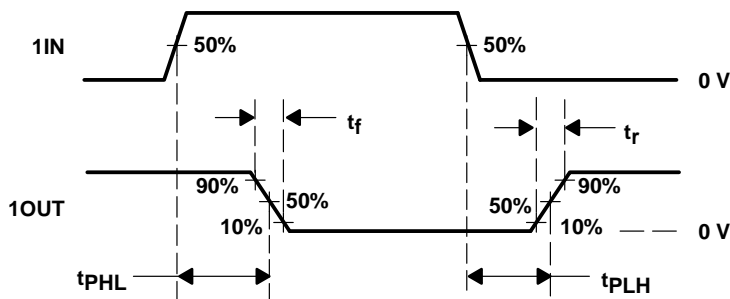


Figure 3. Typical Timing Diagram (TPS2811)

TYPICAL CHARACTERISTICS

Tables of Characteristics Graphs and Application Information

typical characteristics

| PARAMETER | vs PARAMETER 2 | FIGURE | PAGE |
|-----------------------------|----------------------------|--------|------|
| Rise time | Supply voltage | 4 | 10 |
| Fall time | Supply voltage | 5 | 10 |
| Propagation delay time | Supply voltage | 6, 7 | 10 |
| Supply current | Supply voltage | 8 | 11 |
| | Load capacitance | 9 | 11 |
| | Ambient temperature | 10 | 11 |
| Input threshold voltage | Supply voltage | 11 | 11 |
| Regulator output voltage | Regulator input voltage | 12, 13 | 12 |
| Regulator quiescent current | Regulator input voltage | 14 | 12 |
| Peak source current | Supply voltage | 15 | 12 |
| Peak sink current | Supply voltage | 16 | 13 |
| Shoot-through current | Input voltage, high-to-low | 17 | 13 |
| | Input voltage, low-to-high | 18 | 13 |

TYPICAL CHARACTERISTICS

Tables of Characteristics Graphs and Application Information (Continued)

general applications

| PARAMETER | vs PARAMETER 2 | FIGURE | PAGE |
|---|----------------|-------------|--------|
| Switching test circuits and application information | | 19, 20 | 15 |
| Voltage of 1OUT vs 2OUT | Time | Low-to-high | 16, 17 |
| | | High-to-low | 16, 17 |

circuit for measuring paralleled switching characteristics

| PARAMETER | vs PARAMETER 2 | FIGURE | PAGE |
|---|----------------|-------------|------|
| Switching test circuits and application information | | 27 | 17 |
| Input voltage vs output voltage | Time | Low-to-high | 18 |
| | | High-to-low | 18 |

Hex-1 to Hex-4 application information

| PARAMETER | vs PARAMETER 2 | FIGURE | PAGE |
|---|----------------|---------------------------|------|
| Driving test circuit and application information | | 32 | 19 |
| Drain-source voltage vs drain current | Time | Hex-1 size | 20 |
| | | Hex-2 size | 20 |
| | | Hex-3 size | 21 |
| | | Hex-4 size | 22 |
| | | Hex-4 size parallel drive | 23 |
| Drain-source voltage vs gate-source voltage at turn-on | Time | Hex-1 size | 20 |
| | | Hex-2 size | 21 |
| | | Hex-3 size | 21 |
| | | Hex-4 size | 22 |
| | | Hex-4 size parallel drive | 23 |
| Drain-source voltage vs gate-source voltage at turn-off | Time | Hex-1 size | 20 |
| | | Hex-2 size | 21 |
| | | Hex-3 size | 22 |
| | | Hex-4 size | 22 |
| | | Hex-4 size parallel drive | 23 |

synchronous buck regulator application

| PARAMETER | vs PARAMETER 2 | FIGURE | PAGE |
|--|----------------|------------|--------|
| 3.3-V 3-A Synchronous-Rectified Buck Regulator Circuit | | 48 | 24 |
| Q1 drain voltage vs gate voltage at turn-on | Time | 49 | 26 |
| Q1 drain voltage vs gate voltage at turn-off | | 50 | 26 |
| Q1 drain voltage vs Q2 gate-source voltage | | 51, 52, 53 | 26, 27 |
| Output ripple voltage vs inductor current | | 3 A | 27 |
| | | 5 A | 27 |

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TYPICAL CHARACTERISTICS

**RISE TIME
vs
SUPPLY VOLTAGE**

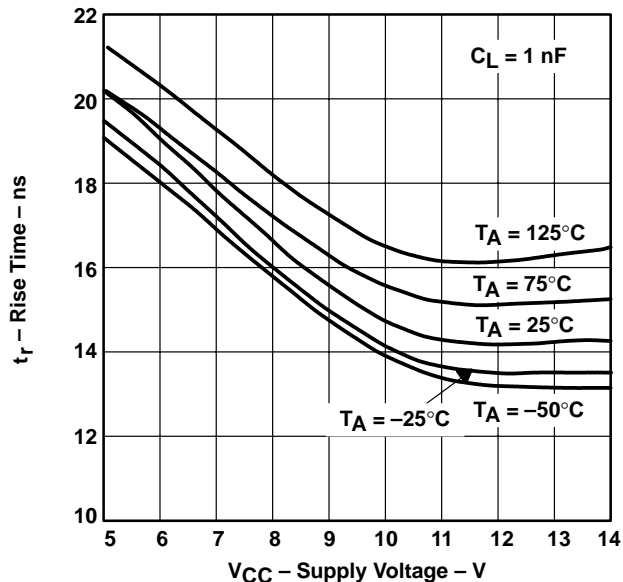


Figure 4

**FALL TIME
vs
SUPPLY VOLTAGE**

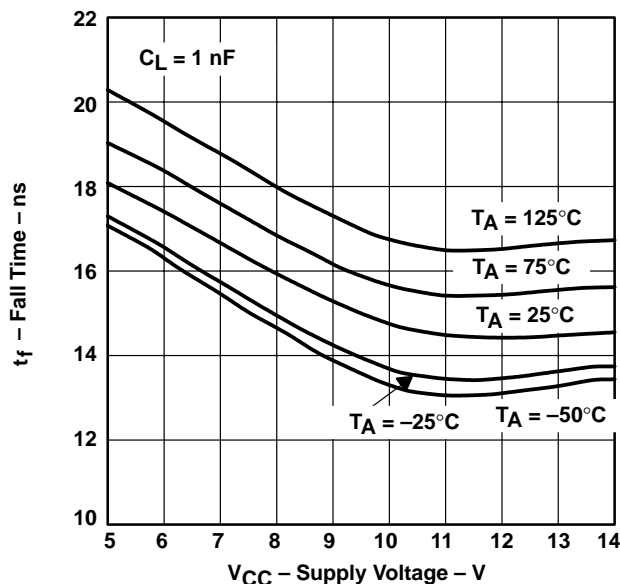


Figure 5

**PROPAGATION DELAY TIME,
HIGH-TO-LOW-LEVEL OUTPUT
vs
SUPPLY VOLTAGE**

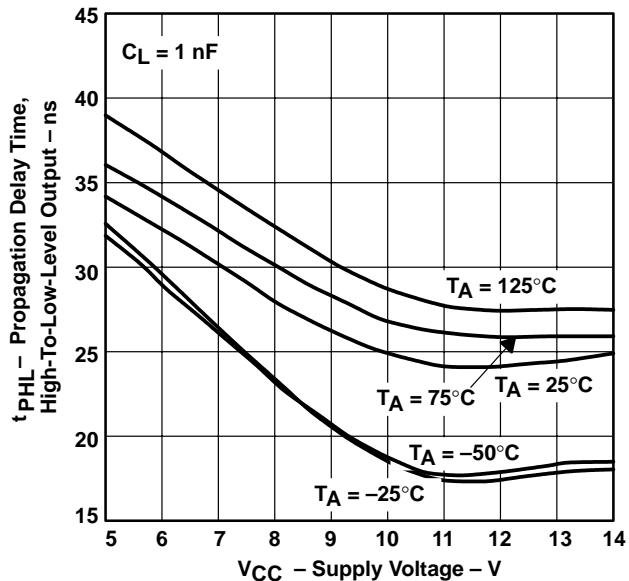


Figure 6

**PROPAGATION DELAY TIME,
LOW-TO-HIGH-LEVEL OUTPUT
vs
SUPPLY VOLTAGE**

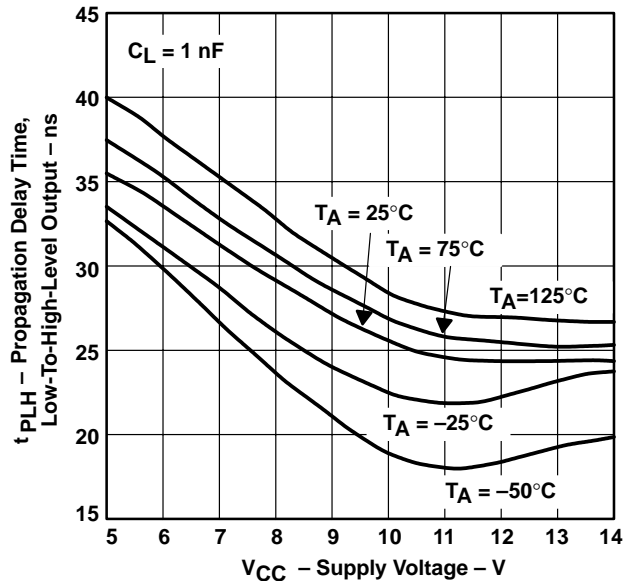


Figure 7

TYPICAL CHARACTERISTICS

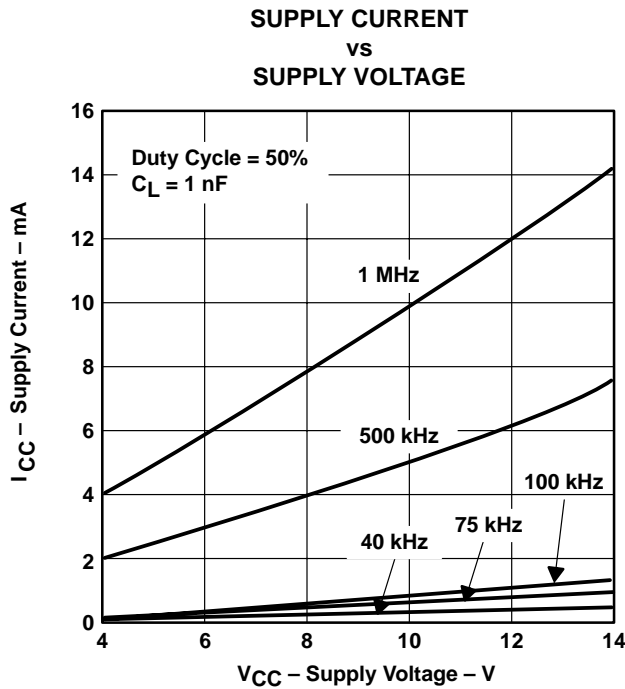


Figure 8

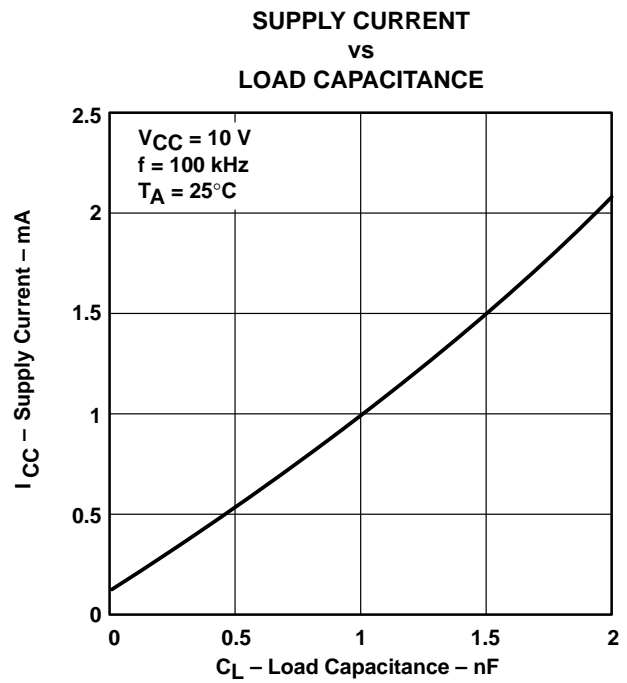


Figure 9

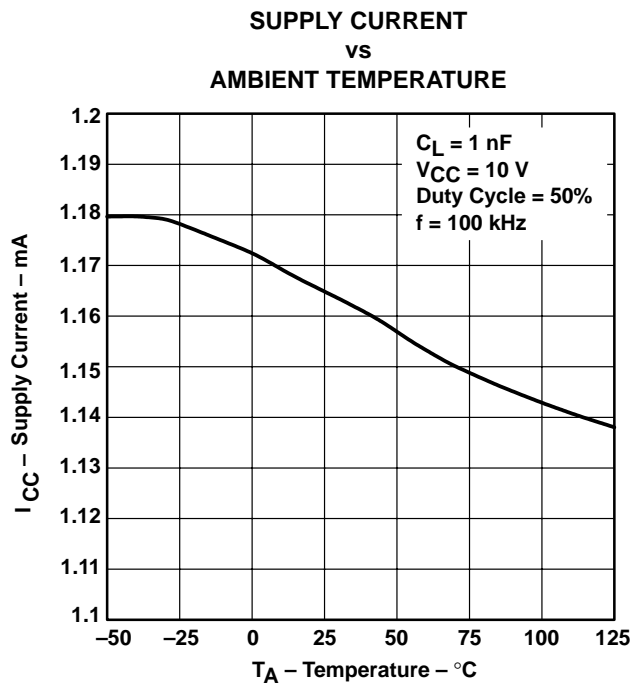


Figure 10

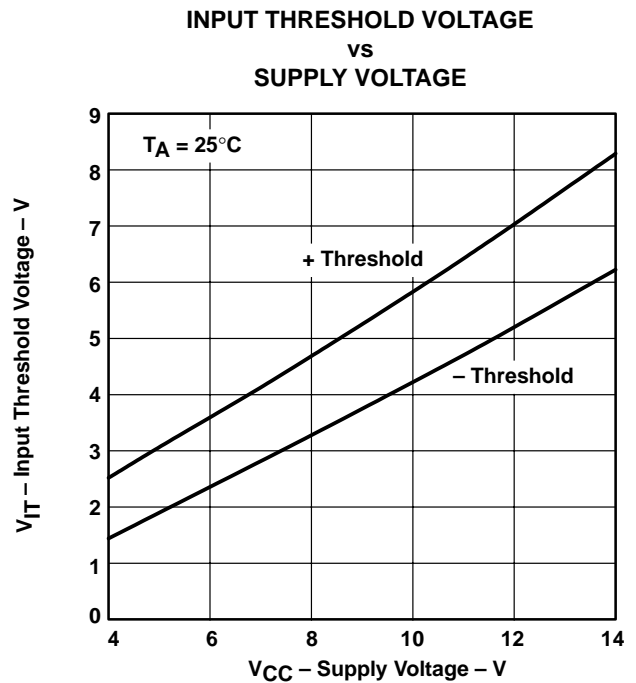


Figure 11

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

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TYPICAL CHARACTERISTICS

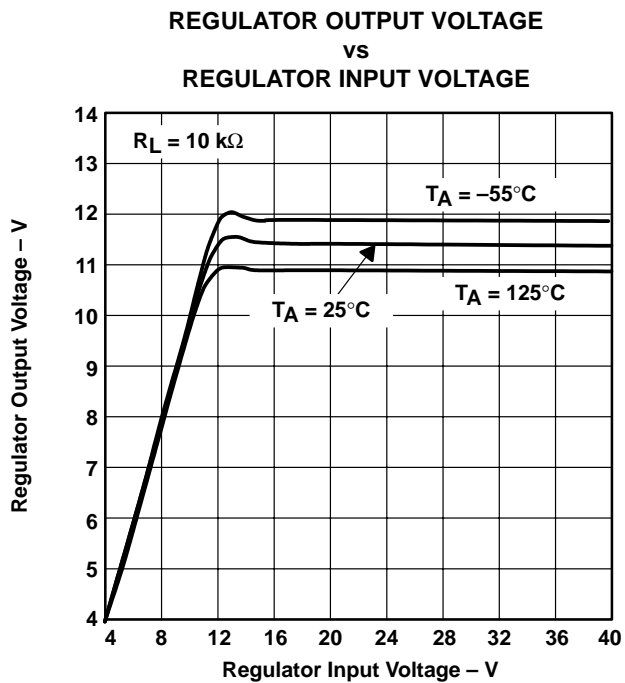


Figure 12

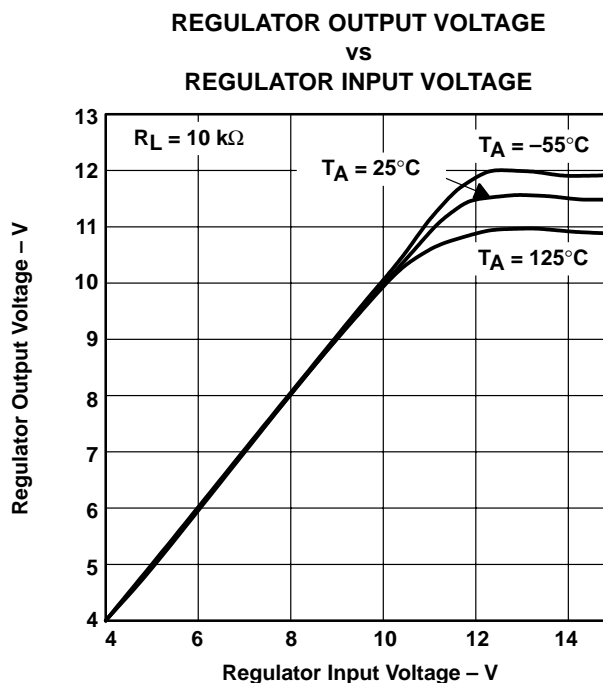


Figure 13

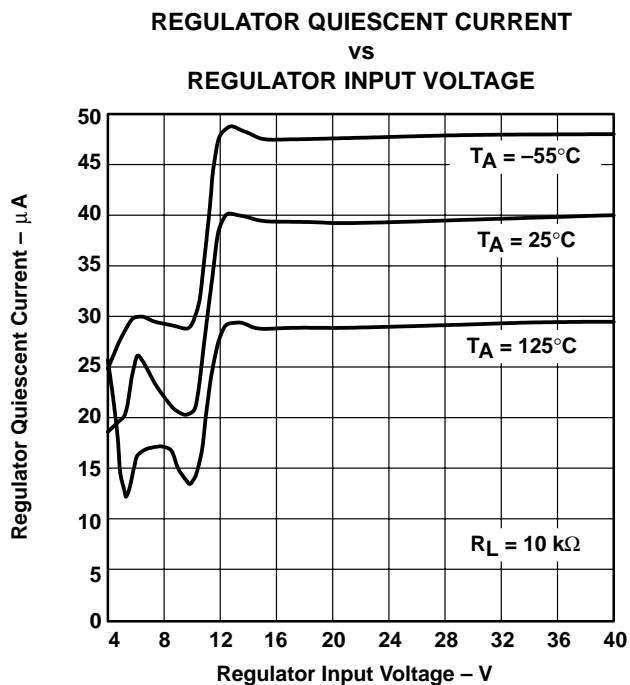


Figure 14

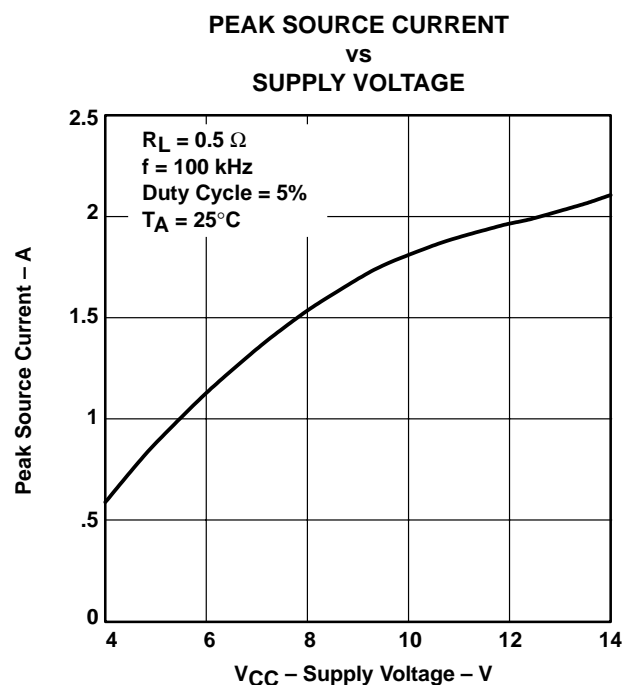


Figure 15

TYPICAL CHARACTERISTICS

PEAK SINK CURRENT
 vs
 SUPPLY VOLTAGE

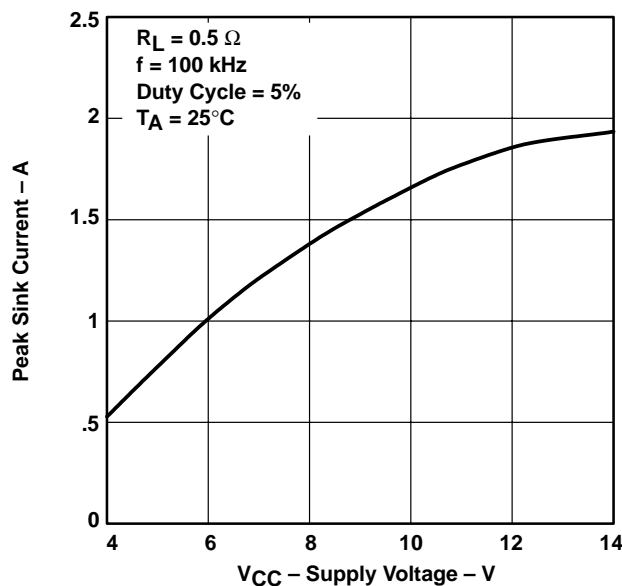


Figure 16

SHOOT-THROUGH CURRENT
 vs
 INPUT VOLTAGE, HIGH-TO-LOW

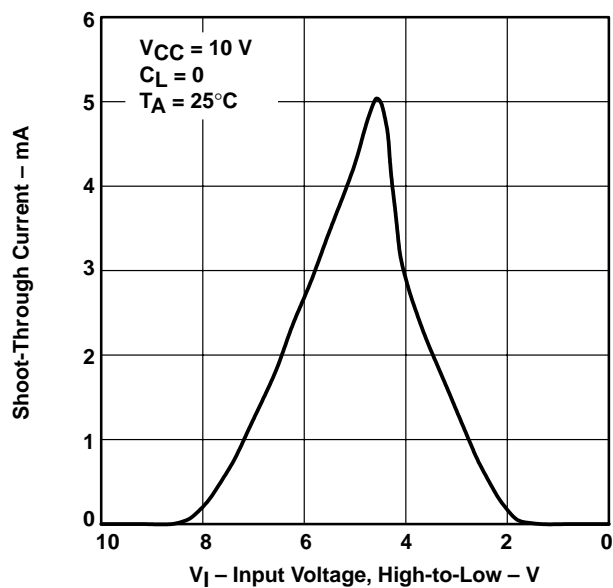


Figure 17

SHOOT-THROUGH CURRENT
 vs
 INPUT VOLTAGE, LOW-TO-HIGH

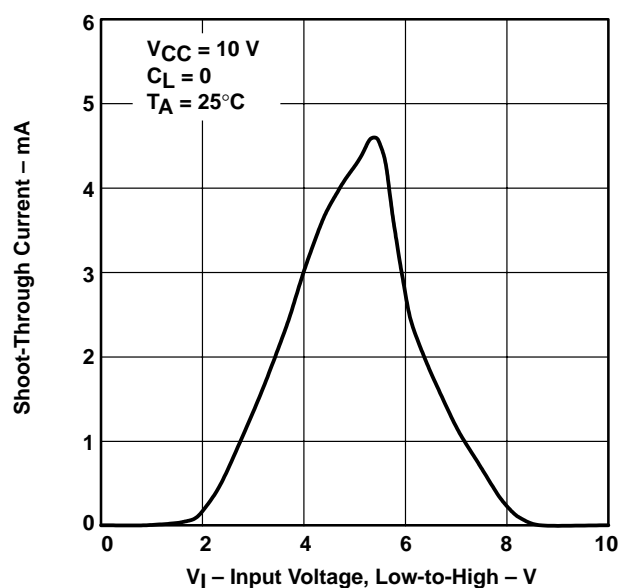


Figure 18

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

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APPLICATION INFORMATION

The TPS2811, TPS2812 and TPS2813 circuits each contain one regulator and two MOSFET drivers. The regulator can be used to limit V_{CC} to between 10 V and 13 V for a range of input voltages from 14 V to 40 V, while providing up to 20 mA of dc drive. The TPS2814 and TPS2815 both contain two drivers, each of which has two inputs. The TPS2811 has inverting drivers, the TPS2812 has noninverting drivers, and the TPS2813 has one inverting and one noninverting driver. The TPS2814 is a dual 2-input AND driver with one inverting input on each driver, and the TPS2815 is a dual 2-input NAND driver. These MOSFET drivers are capable of supplying up to 2.1 A or sinking up to 1.9 A (see Figures 15 and 16) of instantaneous current to n-channel or p-channel MOSFETs. The TPS2811 family of MOSFET drivers have very fast switching times combined with very short propagation delays. These features enhance the operation of today's high-frequency circuits.

The CMOS input circuit has a positive threshold of approximately 2/3 of V_{CC} , with a negative threshold of 1/3 of V_{CC} , and a very high input impedance in the range of $10^9 \Omega$. Noise immunity is also very high because of the Schmidt trigger switching. In addition, the design is such that the normal shoot-through current in CMOS (when the input is biased halfway between V_{CC} and ground) is limited to less than 6 mA. The limited shoot-through is evident in the graphs in Figures 17 and 18. The input stage shown in the functional block diagram better illustrates the way the front end works. The circuitry of the device is such that regardless of the rise and/or fall time of the input signal, the output signal will always have a fast transition speed; this basically isolates the waveforms at the input from the output. Therefore, the specified switching times are not affected by the slopes of the input waveforms.

The basic driver portion of the circuits operate over a supply voltage range of 4 V to 14 V with a maximum bias current of 5 μ A. Each driver consists of a CMOS input and a buffered output with a 2-A instantaneous drive capability. They have propagation delays of less than 30 ns and rise and fall times of less than 20 ns each. Placing a 0.1- μ F ceramic capacitor between V_{CC} and ground is recommended; this will supply the instantaneous current needed by the fast switching and high current surges of the driver when it is driving a MOSFET.

The output circuit is also shown in the functional block diagram. This driver uses a unique combination of a bipolar transistor in parallel with a MOSFET for the ability to swing from V_{CC} to ground while providing 2 A of instantaneous driver current. This unique parallel combination of bipolar and MOSFET output transistors provides the drive required at V_{CC} and ground to guarantee turn-off of even low-threshold MOSFETs. Typical bipolar-only output devices don't easily approach V_{CC} or ground.

The regulator, included in the TPS2811, TPS2812 and TPS2813, has an input voltage range of 14 V to 40 V. It produces an output voltage of 10 V to 13 V and is capable of supplying from 0 to 20 mA of output current. In grounded source applications, this extends the overall circuit operation to 40 V by clamping the driver supply voltage (V_{CC}) to a safe level for both the driver and the MOSFET gate. The bias current for full operation is a maximum of 150 μ A. A 0.1- μ F capacitor connected between the regulator output and ground is required to ensure stability. For transient response, an additional 4.7- μ F electrolytic capacitor on the output and a 0.1- μ F ceramic capacitor on the input will optimize the performance of this circuit. When the regulator is not in use, it can be left open at both the input and the output, or the input can be shorted to the output and tied to either the V_{CC} or the ground pin of the chip.

APPLICATION INFORMATION

matching and paralleling connections

Figures 21 and 22 show the delays for the rise and fall time of each channel. As can be seen on a 5-ns scale, there is very little difference between the two channels at no load. Figures 23 and 24 show the difference between the two channels for a 1-nF load on each output. There is a slight delay on the rising edge, but little or no delay on the falling edge. As an example of extreme overload, Figures 25 and 26 show the difference between the two channels, or two drivers in the package, each driving a 10-nF load. As would be expected, the rise and fall times are significantly slowed down. Figures 28 and 29 show the effect of paralleling the two channels and driving a 1-nF load. A noticeable improvement is evident in the rise and fall times of the output waveforms. Finally, Figures 30 and 31 show the two drivers being paralleled to drive the 10-nF load and as could be expected the waveforms are improved. In summary, the paralleling of the two drivers in a package enhances the capability of the drivers to handle a larger load. Because of manufacturing tolerances, it is not recommended to parallel drivers that are not in the same package.

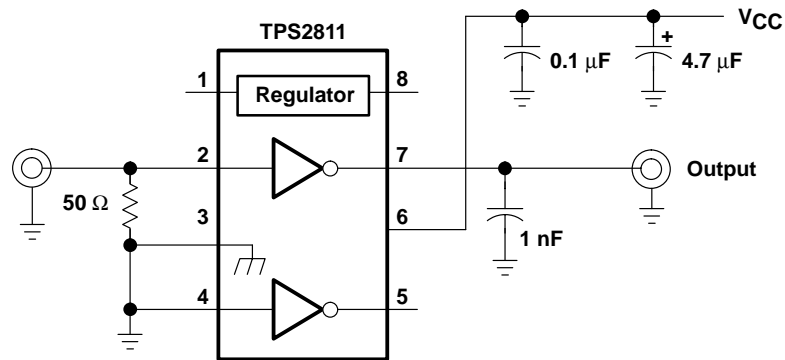
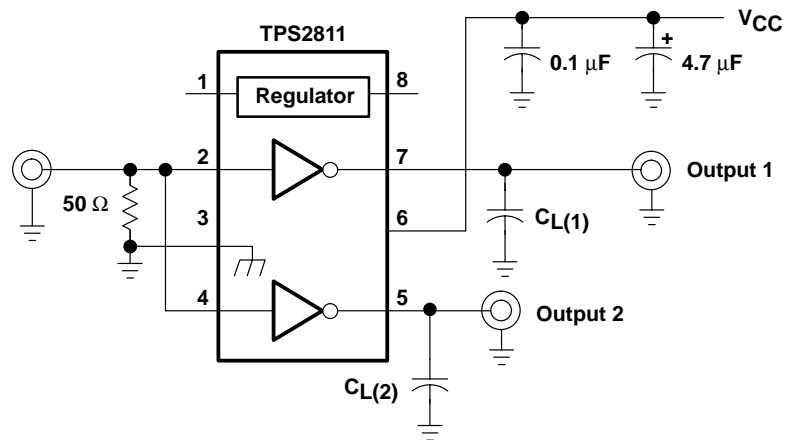


Figure 19. Test Circuit for Measuring Switching Characteristics



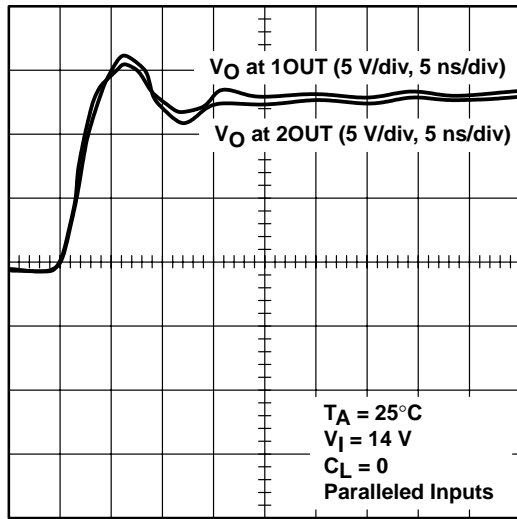
NOTE A: Input rise and fall times should be ≤ 10 ns for accurate measurement of ac parameters.

Figure 20. Test Circuit for Measuring Switching Characteristics with the Inputs Connected in Parallel

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

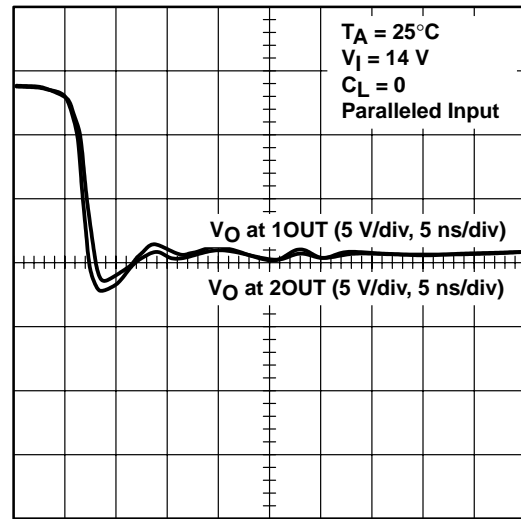
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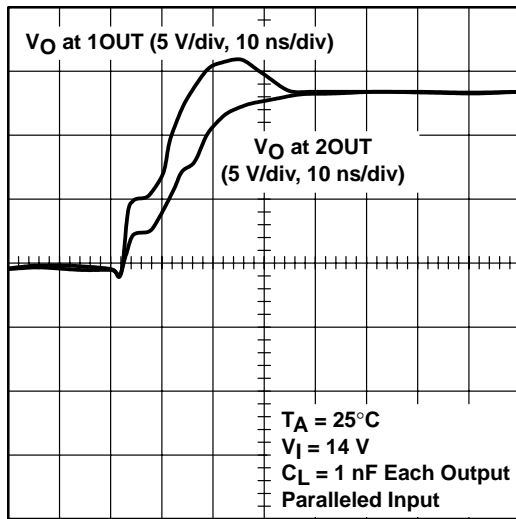
t – Time

Figure 21. Voltage of 1OUT vs Voltage at 2OUT, Low-to-High Output Delay



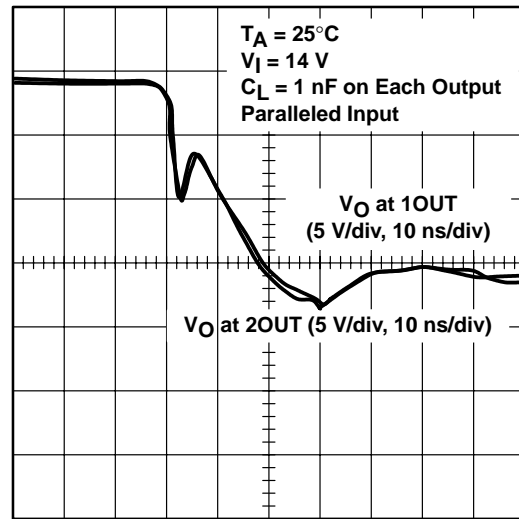
t – Time

Figure 22. Voltage at 1OUT vs Voltage at 2OUT, High-to-Low Output Delay



t – Time

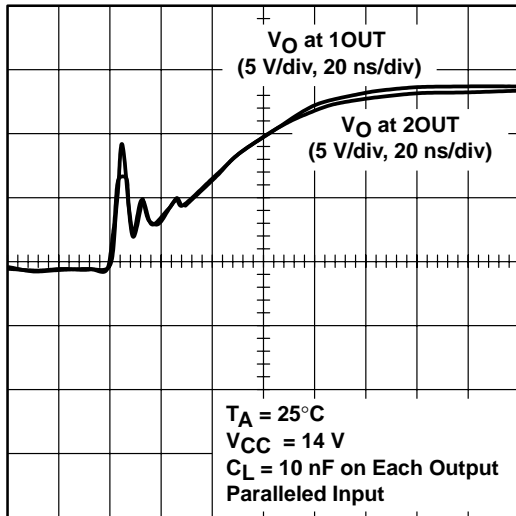
Figure 23. Voltage at 1OUT vs Voltage at 2OUT, Low-to-High Output Delay



t – Time

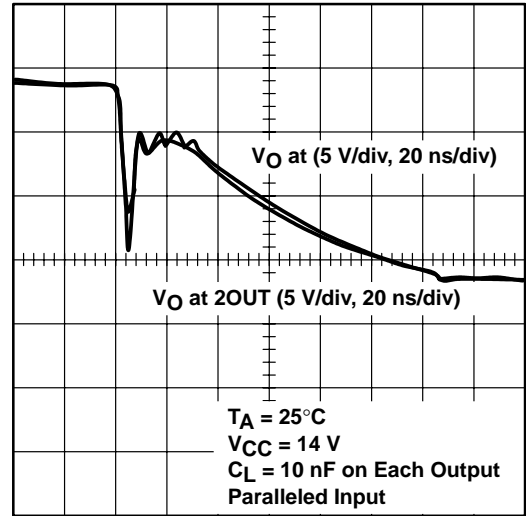
Figure 24. Voltage at 1OUT vs Voltage at 2OUT, High-to-Low Output Delay

APPLICATION INFORMATION



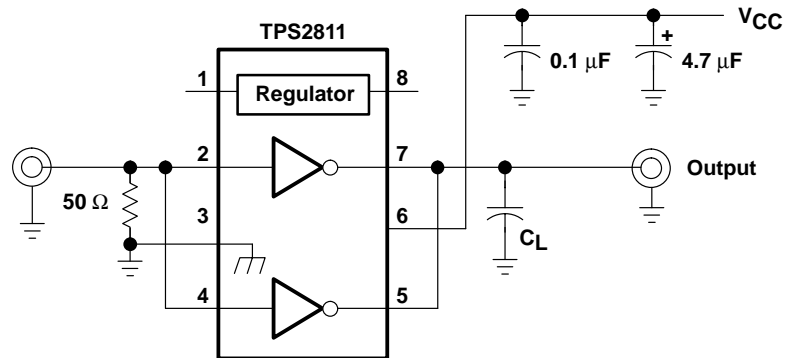
t – Time

Figure 25. Voltage at 1OUT vs Voltage at 2OUT, Low-to-High Output Delay



t – Time

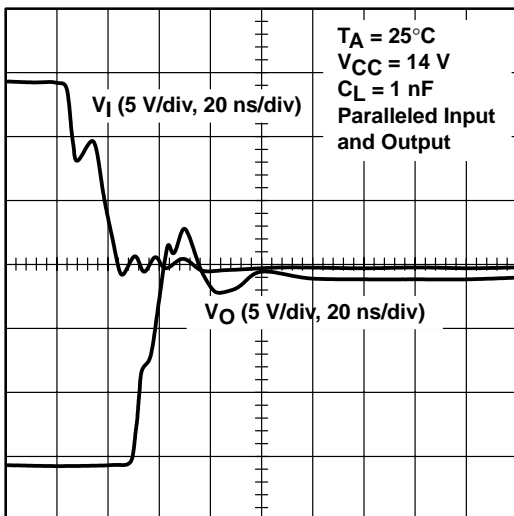
Figure 26. Voltage at 1OUT vs Voltage at 2OUT, High-to-Low Output Delay



NOTE A: Input rise and fall times should be ≤ 10 ns for accurate measurement of ac parameters.

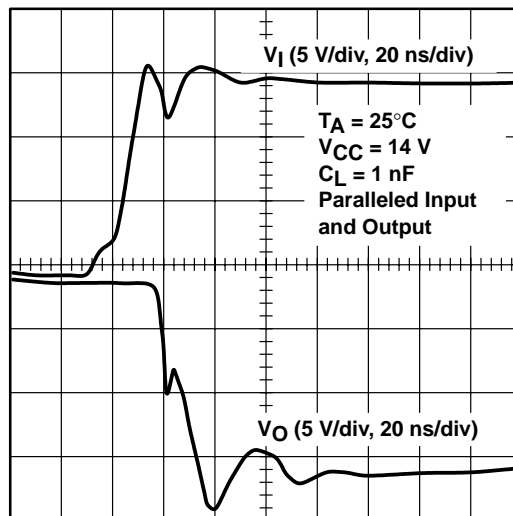
Figure 27. Test Circuit for Measuring Paralleled Switching Characteristics

APPLICATION INFORMATION



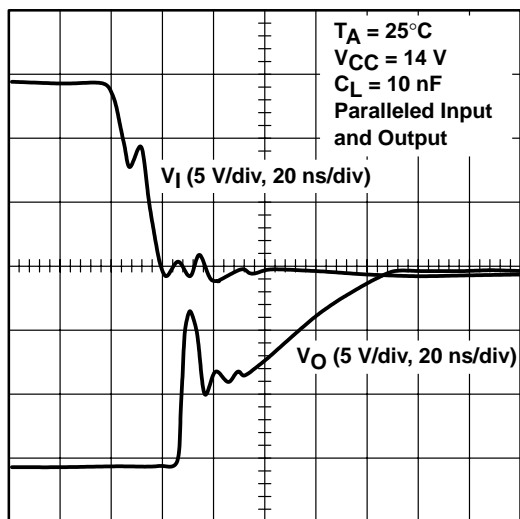
t – Time

Figure 28. Input Voltage vs Output Voltage, Low-to-High Propagation Delay of Paralleled Drivers



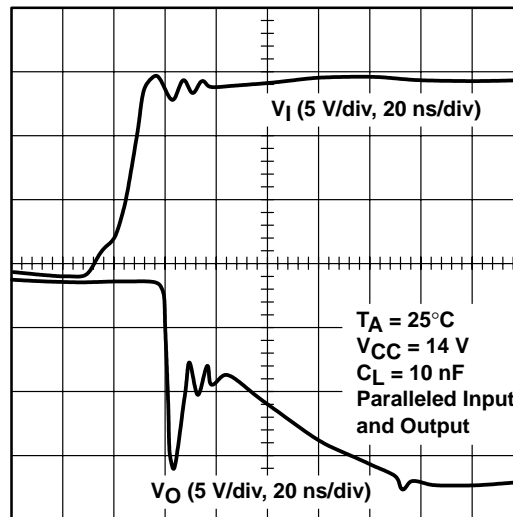
t – Time

Figure 29. Input Voltage vs Output Voltage, High-to-Low Propagation Delay of Paralleled Drivers



t – Time

Figure 30. Input Voltage vs Output Voltage, Low-to-High Propagation Delay of Paralleled Drivers



t – Time

Figure 31. Input Voltage vs Output Voltage, High-to-Low Propagation Delay of Paralleled Drivers

APPLICATION INFORMATION

Figures 33 through 47 illustrate the performance of the TPS2811 driving MOSFETs with clamped inductive loads, similar to what is encountered in discontinuous-mode flyback converters. The MOSFETs that were tested range in size from Hex-1 to Hex-4, although the TPS28xx family is only recommended for Hex-3 or below.

The test circuit is shown in Figure 32. The layout rules observed in building the test circuit also apply to real applications. Decoupling capacitor C1 is a 0.1- μ F ceramic device, connected between V_{CC} and GND of the TPS2811, with short lead lengths. The connection between the driver output and the MOSFET gate, and between GND and the MOSFET source, are as short as possible to minimize inductance. Ideally, GND of the driver is connected directly to the MOSFET source. The tests were conducted with the pulse generator frequency set very low to eliminate the need for heat sinking, and the duty cycle was set to turn off the MOSFET when the drain current reached 50% of its rated value. The input voltage was adjusted to clamp the drain voltage at 80% of its rating.

As shown, the driver is capable of driving each of the Hex-1 through Hex-3 MOSFETs to switch in 20 ns or less. Even the Hex-4 is turned on in less than 20 ns. Figures 45, 46 and 47 show that paralleling the two drivers in a package enhances the gate waveforms and improves the switching speed of the MOSFET. Generally, one driver is capable of driving up to a Hex-4 size. The TPS2811 family is even capable of driving large MOSFETs that have a low gate charge.

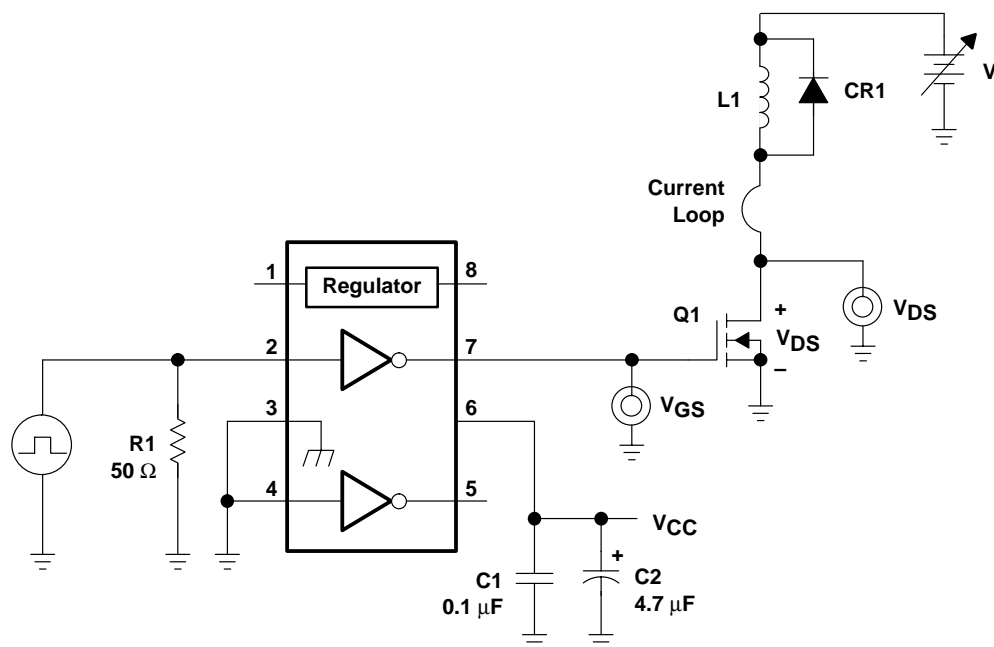
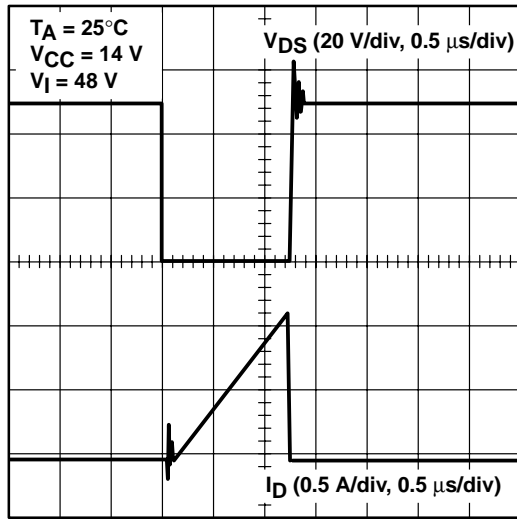


Figure 32. TPS2811 Driving Hex-1 through Hex-4 Devices

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

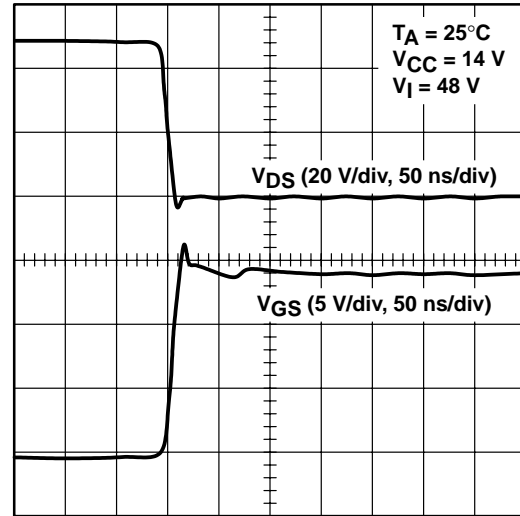
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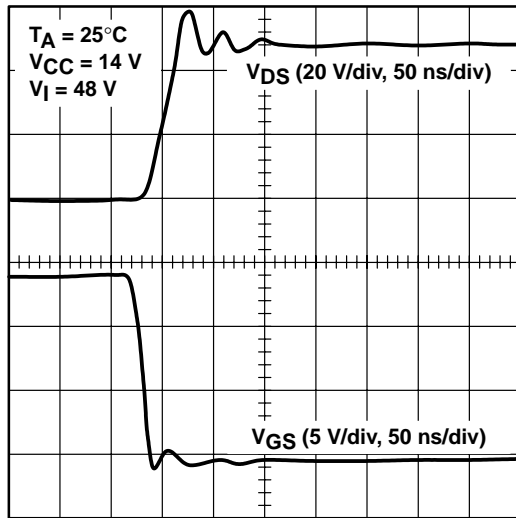
t – Time

Figure 33. Drain-Source Voltage vs Drain Current, TPS2811 Driving an IRFD014 (Hex-1 Size)



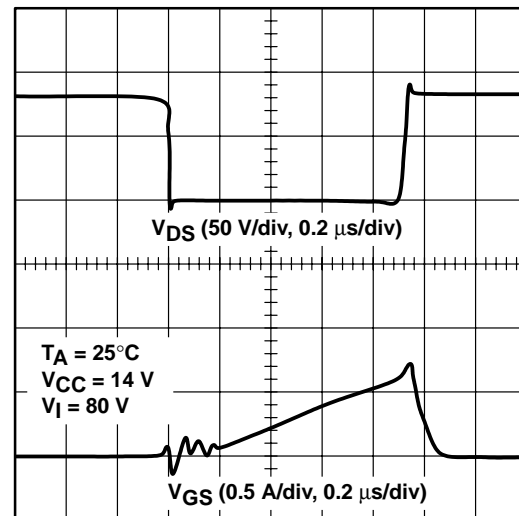
t – Time

Figure 34. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, TPS2811 Driving an IRFD014 (Hex-1 Size)



t – Time

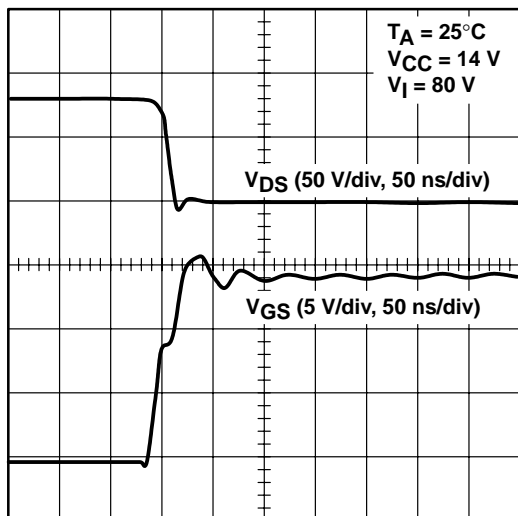
Figure 35. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, TPS2811 Driving an IRFD014 (Hex-1 Size)



t – Time

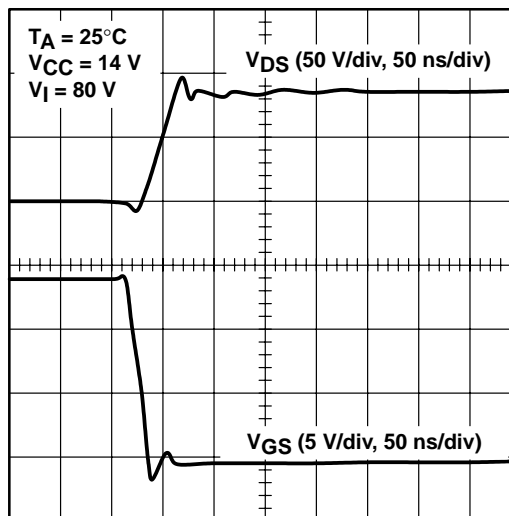
Figure 36. Drain-Source Voltage vs Drain Current, TPS2811 Driving an IRFD120 (Hex-2 Size)

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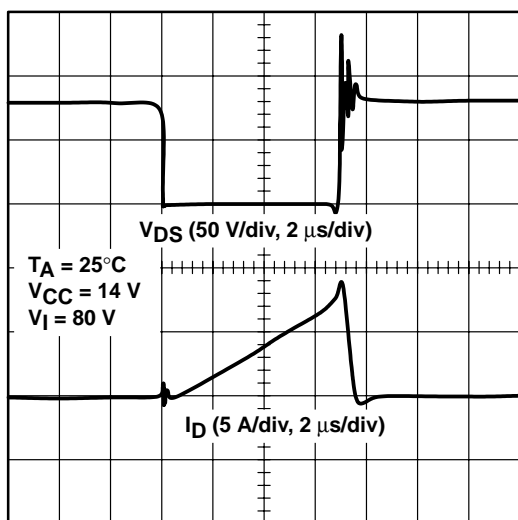
t – Time

Figure 37. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, TPS2811 Driving an IRFD120 (Hex-2 Size)



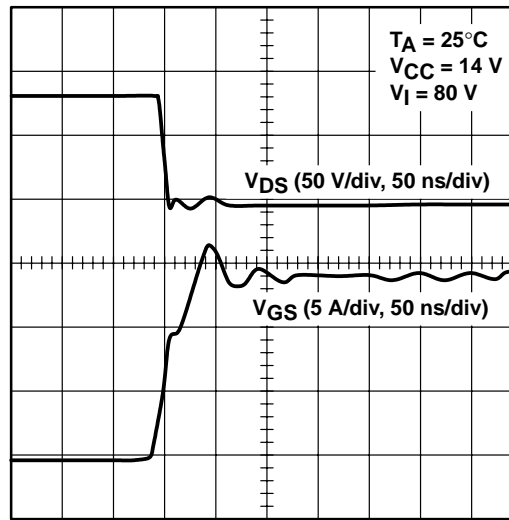
t – Time

Figure 38. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, TPS2811 Driving an IRFD120 (Hex-2 Size)



t – Time

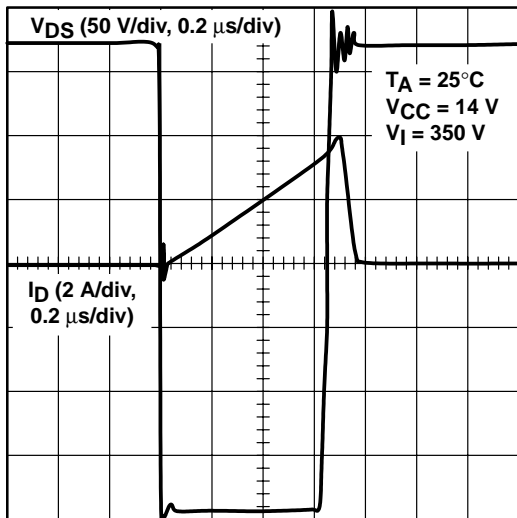
Figure 39. Drain-Source Voltage vs Drain Current, TPS2811 Driving an IRF530 (Hex-3 Size)



t – Time

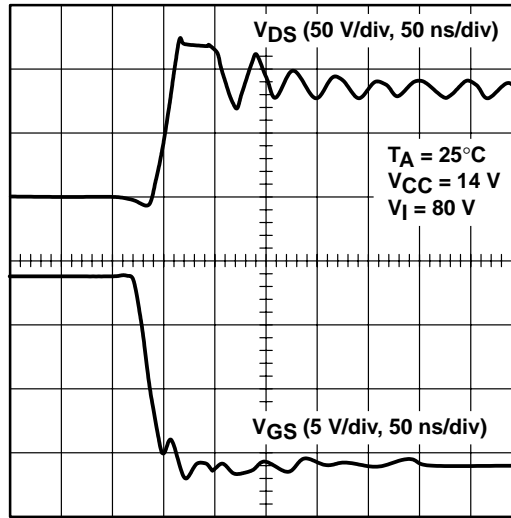
Figure 40. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, TPS2811 Driving an IRF530 (Hex-3 Size)

APPLICATION INFORMATION



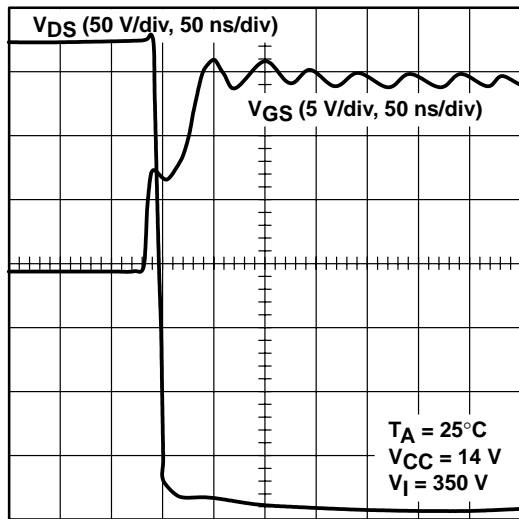
t – Time

Figure 41. Drain-Source Voltage vs Drain Current, One Driver, TPS2811 Driving an IRF840 (Hex-4 Size)



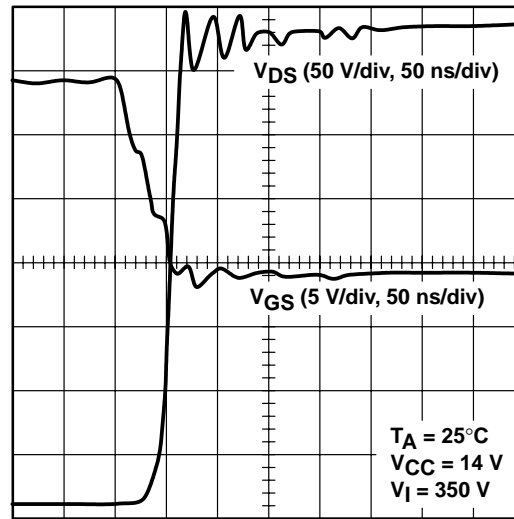
t – Time

Figure 42. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, TPS2811 Driving an IRF530 (Hex-3 Size)



t – Time

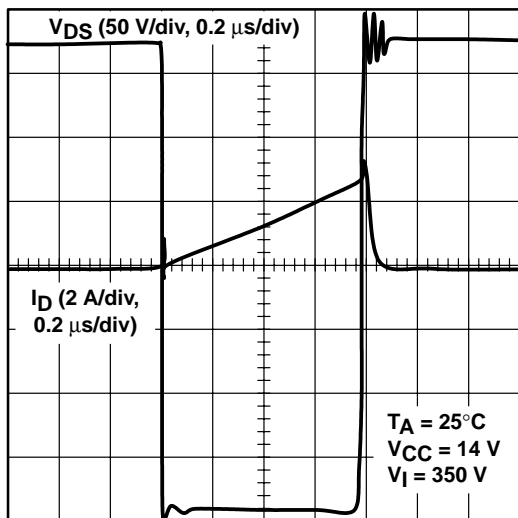
Figure 43. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, One Driver, TPS2811 Driving an IRF840 (Hex-4 Size)



t – Time

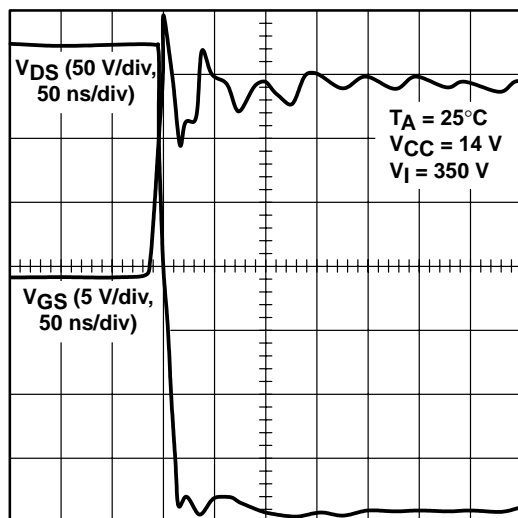
Figure 44. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, One Driver, TPS2811 Driving an IRF840 (Hex-4 Size)

APPLICATION INFORMATION



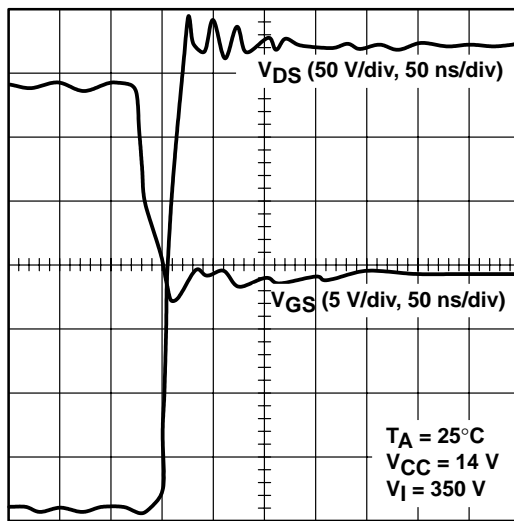
t – Time

Figure 45. Drain-Source Voltage vs Drain Current, Parallel Drivers, TPS2811 Driving an IRF840 (Hex-4 Size)



t – Time

Figure 46. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, Parallel Drivers, TPS2811 Driving an IRF840 (Hex-4 Size)



t – Time

Figure 47. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, Parallel Drivers, TPS2811 Driving an IRF840 (Hex-4 Size)

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

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APPLICATION INFORMATION

synchronous buck regulator

Figure 48 is the schematic for a 100-kHz synchronous-rectified buck converter implemented with a TL5001 pulse-width-modulation (PWM) controller and a TPS2812 driver. The bill of materials is provided in Table 1. The converter operates over an input range from 5.5 V to 12 V and has a 3.3-V output capable of supplying 3 A continuously and 5 A during load surges. The converter achieves an efficiency of 90.6% at 3 A and 87.6% at 5 A. Figures 49 and 50 show the power switch switching performance. The output ripple voltage waveforms are documented in Figures 54 and 55.

The TPS2812 drives both the power switch, Q2, and the synchronous rectifier, Q1. Large shoot-through currents, caused by power switch and synchronous rectifier remaining on simultaneously during the transitions, are prevented by small delays built into the drive signals, using CR2, CR3, R11, R12, and the input capacitance of the TPS2812. These delays allow the power switch to turn off before the synchronous rectifier turns on and vice versa. Figure 51 shows the delay between the drain of Q2 and the gate of Q1; expanded views are provided in Figures 52 and 53.

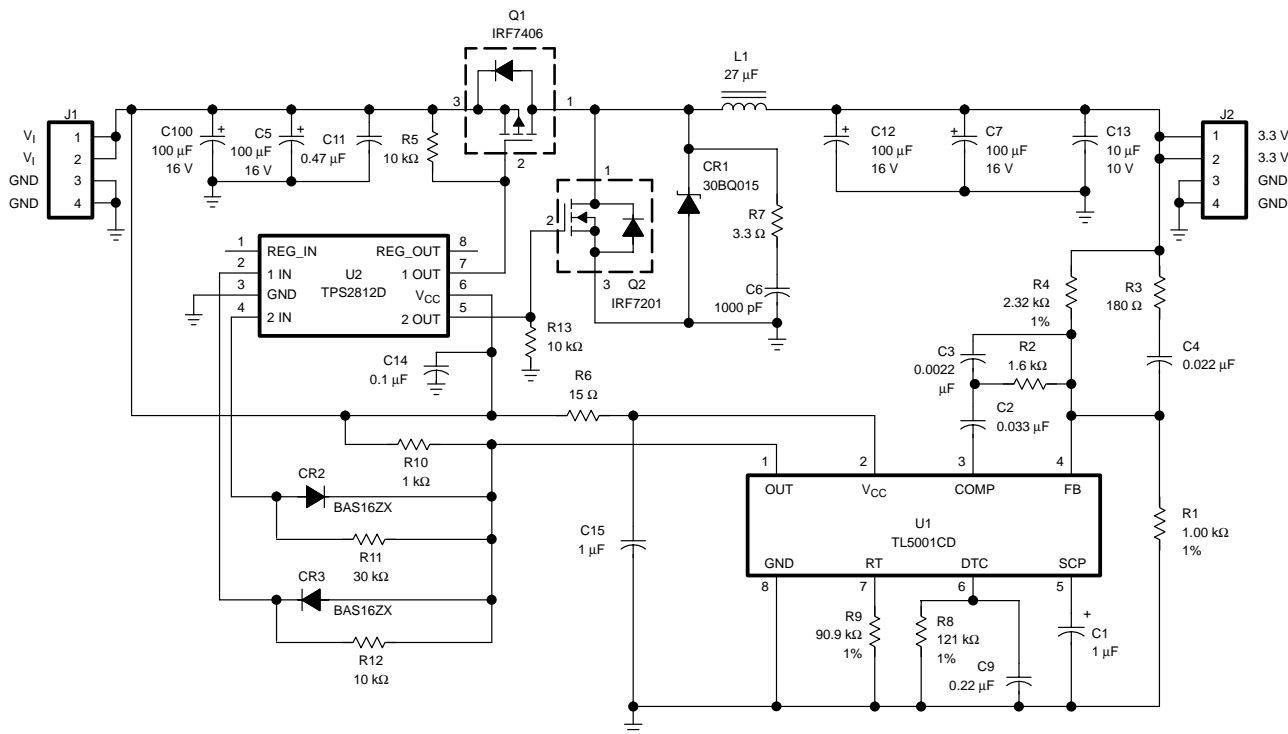


Figure 48. 3.3-V 3-A Synchronous-Rectified Buck Regulator Circuit

NOTE: If the parasitics of the external circuit cause the voltage to violate the Absolute Maximum Rating for the Output pins, Schottky diodes should be added from ground to output and from output to Vcc.

APPLICATION INFORMATION

**Table 1. Bill of Materials,
 3.3-V, 3-A Synchronous-Rectified Buck Converter**

| REFERENCE | DESCRIPTION | VENDOR |
|---------------|---|---------------------------------------|
| U1 | TL5001CD, PWM | Texas Instruments, 972-644-5580 |
| U2 | TPS2812D, N.I. MOSFET Driver | Texas Instruments, 972-644-5580 |
| CR1 | 3 A, 15 V, Schottky, 30BQ015 | International Rectifier, 310-322-3331 |
| CR2,CR3 | Signal Diode, BAS16ZX | Zetex, 516-543-7100 |
| C1 | 1 μ F, 16 V, Tantalum | |
| C2 | 0.033 μ F, 50 V | |
| C3 | 0.0022 μ F, 50 V | |
| C4 | 0.022 μ F, 50 V | |
| C5,C7,C10,C12 | 100 μ F, 16 V, Tantalum, TPSE107M016R0100 | AVX, 800-448-9411 |
| C6 | 1000 pF, 50 V | |
| C9 | 0.22 μ F, 50 V | |
| C11 | 0.47 μ F, 50 V, Z5U | |
| C13 | 10 μ F, 10 V, Ceramic, CC1210CY5V106Z | TDK, 708-803-6100 |
| C14 | 0.1 μ F, 50 V | |
| C15 | 1.0 μ F, 50 V | |
| J1,J2 | 4-Pin Header | |
| L1 | 27 μ H, 3 A/5 A, SML5040 | Nova Magnetics, Inc., 972-272-8287 |
| Q1 | IRF7406, P-FET | International Rectifier, 310-322-3331 |
| Q2 | IRF7201, N-FET | International Rectifier, 310-322-3331 |
| R1 | 1.00 k Ω , 1% | |
| R2 | 1.6 k Ω | |
| R3 | 180 Ω | |
| R4 | 2.32 k Ω , 1 % | |
| R5,R12,R13 | 10 k Ω | |
| R6 | 15 Ω | |
| R7 | 3.3 Ω | |
| R8 | 121 k Ω , 1% | |
| R9 | 90.9 k Ω , 1% | |
| R10 | 1 k Ω | |
| R11 | 30 k Ω | |

NOTES: 2. Unless otherwise specified, capacitors are X7R ceramics.
 3. Unless otherwise specified, resistors are 5%, 1/10 W.

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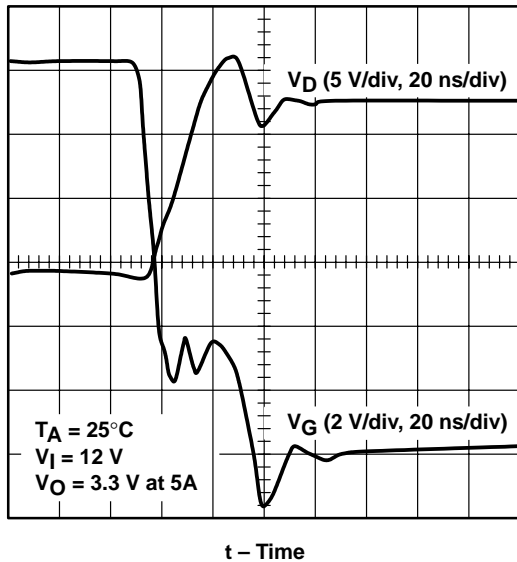


Figure 49. Q1 Drain Voltage vs Gate Voltage, at Switch Turn-on

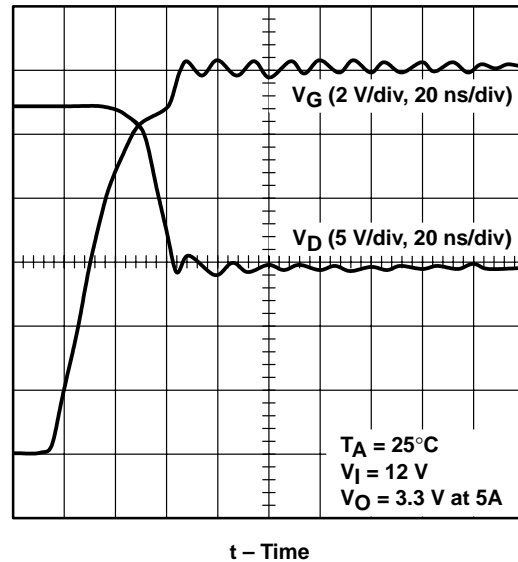


Figure 50. Q1 Drain Voltage vs Gate Voltage, at Switch Turn-off

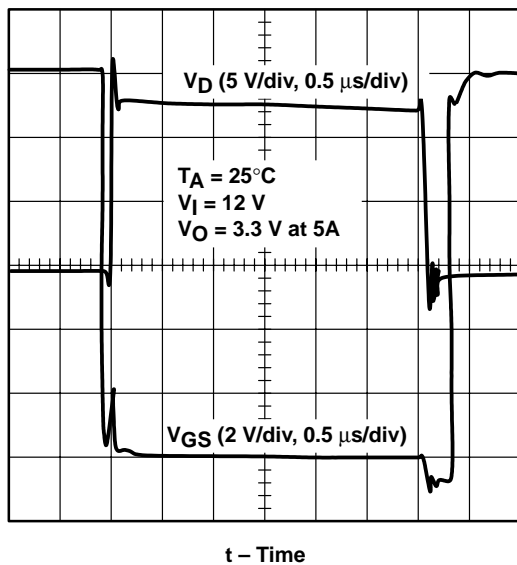


Figure 51. Q1 Drain Voltage vs Q2 Gate-Source Voltage

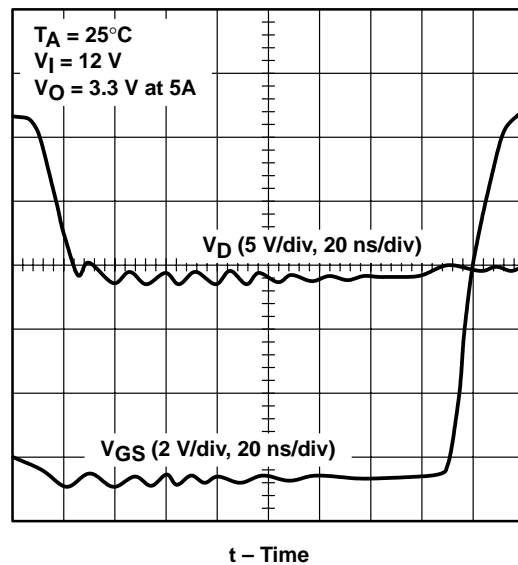


Figure 52. Q1 Drain Voltage vs Q2 Gate-Source Voltage

APPLICATION INFORMATION

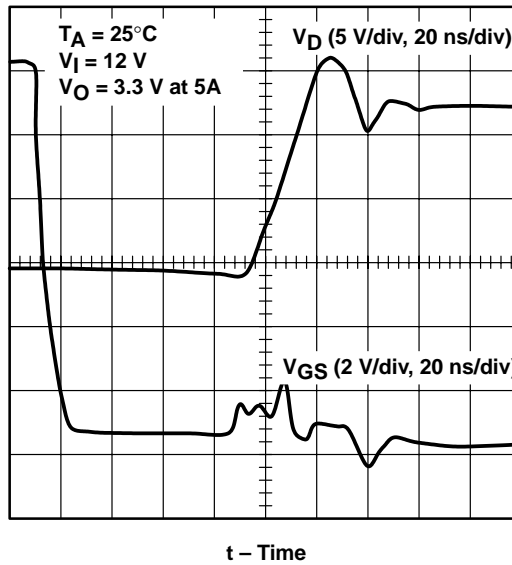


Figure 53. Q1 Drain Voltage vs Q2 Gate-Source Voltage

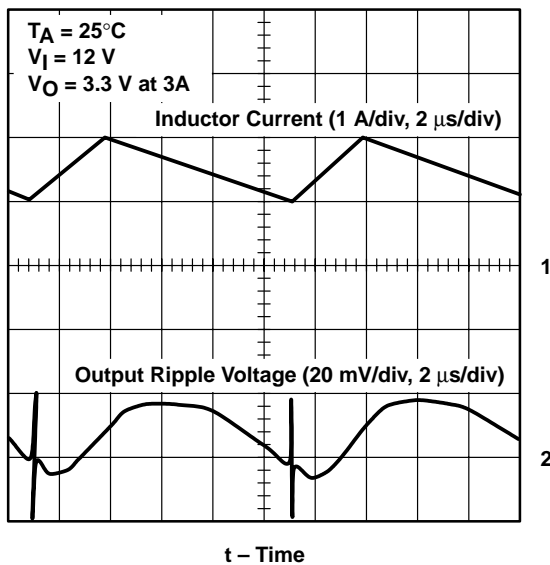


Figure 54. Output Ripple Voltage vs Inductor Current, at 3 A

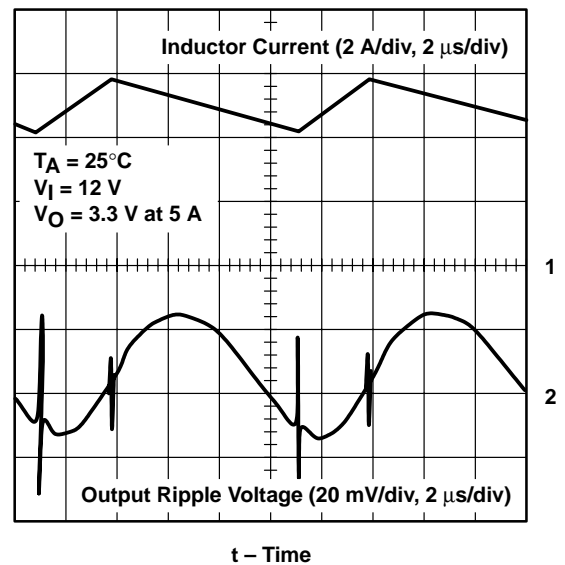


Figure 55. Output Ripple Voltage vs Inductor Current, at 5 A

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

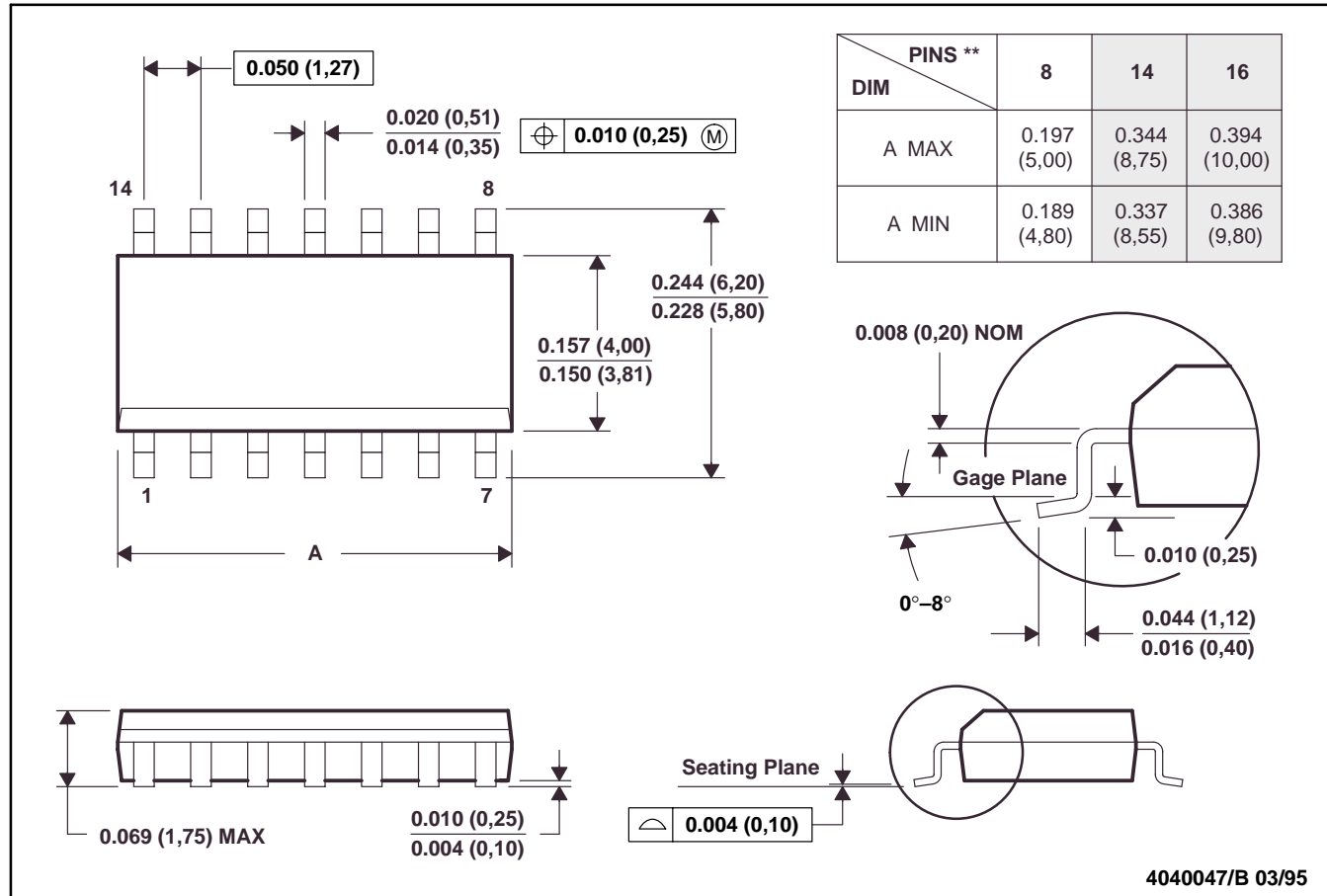
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MECHANICAL DATA

D (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN

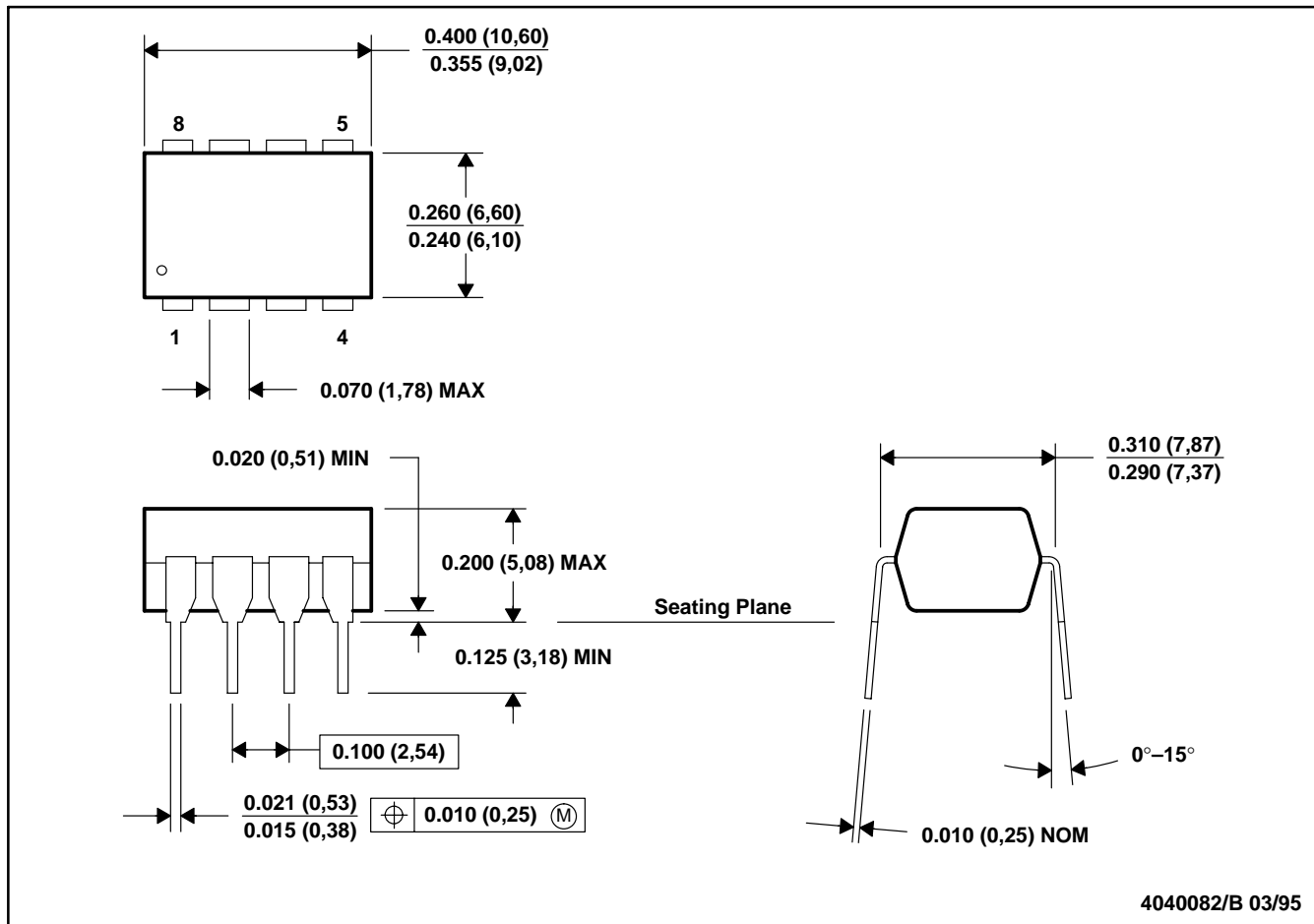


- NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
 D. Four center pins are connected to die mount pad.
 E. Falls within JEDEC MS-012

MECHANICAL DATA

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Falls within JEDEC MS-001

TPS2811, TPS2812, TPS2813, TPS2814, TPS2815 DUAL HIGH-SPEED MOSFET DRIVERS

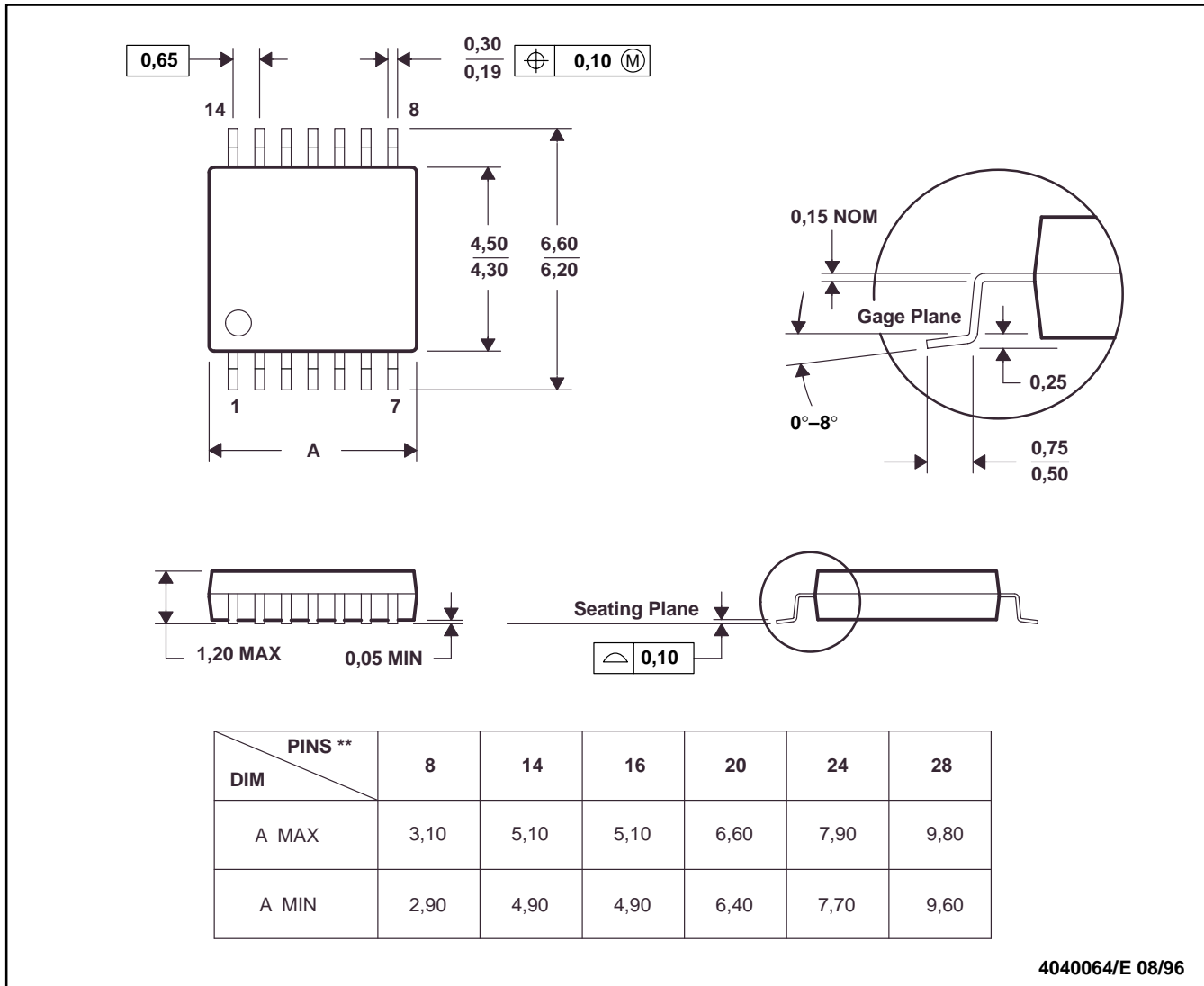
SLVS132E – NOVEMBER 1995 – REVISED OCTOBER 2002

MECHANICAL DATA

PW (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



4040064/E 08/96

- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
 D. Falls within JEDEC MO-153

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